TLV767 1A、16V 精密线性稳压器

1 特性

- V_{IN}：2.5V 至 16V
- V_{OUT}：
  - 0.8V 至 13.6V（可调节）
  - 0.8V 至 6.6V（固定值，50mV 阶跃）
- 在整个负载和温度范围内的输出精度为 1%
- 低 I_Q：50µA（典型值，在关断状态下大约为 1.5µA）
- 内部软启动时间：500µs（典型值）
- 折返电流限制和热保护
- 使用 1µF 陶瓷电容器实现稳定工作
- 高 PSRR：1kHz 频率下为 70dB，1MHz 频率下为 46dB
- 温度范围：–40°C 至 +125°C
- 封装：6 引脚 2mm × 2mm WSON

2 应用

- 电器
- 电视、监控器和机顶盒
- 电机驱动控制板
- 打印机、PC 外设、笔记本电脑、主板
- WiFi 接入点和路由器

3 说明

TLV767 是一种宽输入范围的线性稳压器，支持 2.5V 至 16V 的输入电压范围和高达 1A 的负载电流。输出范围为 0.8V 至 6.6V，在可调版本中输出最高可达 13.6V。

此外，TLV767 的输出精度为 1%，可满足低压微控制器 (MCU) 和处理器的需求。

根据设计，TLV767 的 I_Q 比传统的宽输入电压稳压器低得多，因此该器件能够充分满足日益严格的待机功耗要求。禁用时，TLV767 仅消耗 1.5µA 的 I_Q。

内部软启动时间和折返电流限制可减小启动期间的浪涌电流，从而最大限度降低输入电容。

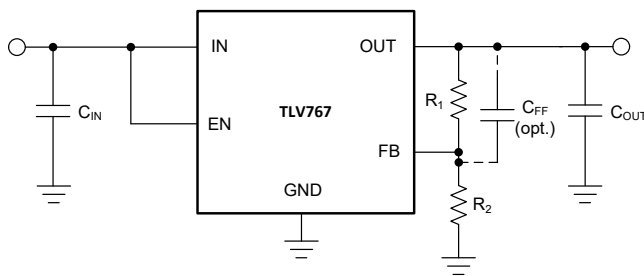高带宽 PSRR 性能在 1kHz 时大于 70dB，在 1MHz 时大于 46dB，因此有助于衰减上游直流/直流转换器的开关频率，并最大限度减少后置稳压器滤波。为了提供更高的灵活性，TLV767 有固定电压和可调电压两种版本可供选用。
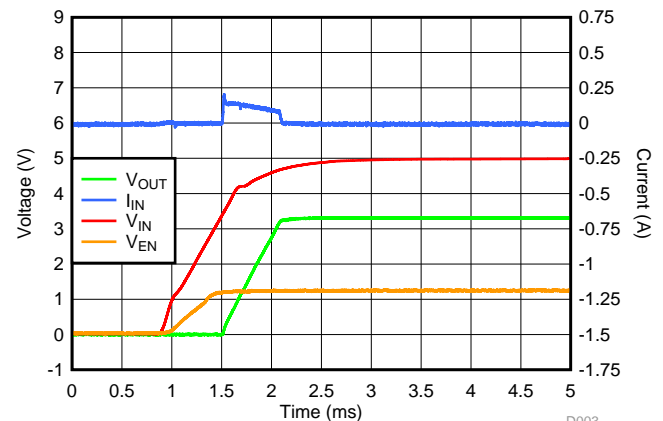
TLV767 采用 6 引脚 2mm × 2mm WSON (DRV) 封装。

器件信息(1)

器件型号	封装	封装尺寸（标称值）
TLV767	WSON (6)	2.00mm × 2.00mm

(1) 如需了解所有可用封装，请参阅产品说明书末尾的可订购产品附录。

典型应用电路

C_{OUT} 为 22µF 时减小的浪涌电流

目录

4 修订历史记录

注：之前版本的页码可能与当前版本有所不同。

Changes from Revision A (December 2018) to Revision B	**Page**
• Added Feedback divider current for adjustable device only... 4	
• Added Dropout voltage footnote for fixed output devices 5	
• Added Quiescent current for fixed output devices.. 5	
• 已更改 order of curves in *Typical Characteristics* to keep key figures side by side.. 7	
• 已添加 condition to V_{OUT} *Accuracy vs* V_{IN} figure 7	
• 已添加 *adjustable-voltage version devices* to condition statement of I_Q *vs* V_{IN} figure... 7	
• 已添加 I_Q *vs Temperature* figure 7	
• 已添加 *in Dropout* to caption of V_{IN} *Transient in Dropout From 4 V to 13 V* figure... 9	

Changes from Original (December 2018) to Revision A	**Page**
• 已更改 状态从"预告信息"更改为"生产数据" 1	

5 Pin Configuration and Functions

DRV Package (Adjustable)
6-Pin WSON
Top View

Not to scale
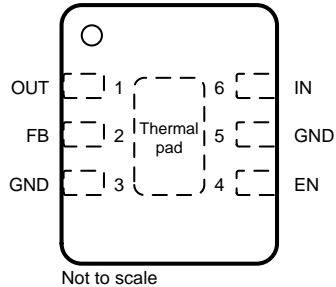
DRV Package (Fixed)
6-Pin WSON
Top View

Not to scale
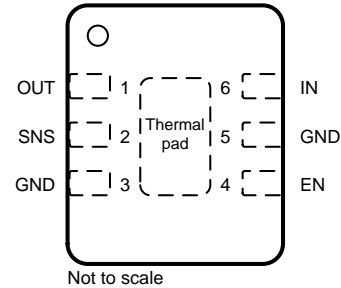
Pin Functions

PIN			I/O	DESCRIPTION
NAME	DRV (Adjustable)	DRV (Fixed)		
EN	4	4	Input	Enable pin. Driving the enable pin high enables the device. Driving this pin low disables the device. High and low thresholds are listed in the *Electrical Characteristics* table. This pin has an internal pullup and can be left floating to enable the device or the pin can be connected to the input pin.
FB	2	—	Input	Feedback pin. Input to the control-loop error amplifier. This pin is used to set the output voltage of the device with the use of external resistors. Do not float this pin. For adjustable-voltage version devices only.
GND	3, 5	3, 5	—	Ground pin. All ground pins must be grounded.
IN	6	6	Input	Input pin. Use the recommended capacitor value as listed in the *Recommended Operating Conditions* table. Place the input capacitor as close to the IN and GND pins of the device as possible.
OUT	1	1	Output	Output pin. Use the recommended capacitor value as listed in the *Recommended Operating Conditions* table. Place the output capacitor as close to the OUT and GND pins of the device as possible.
SNS	—	2	Input	Output sense pin. Connect the SNS pin to the OUT pin, or to remotely sense the output voltage at the load, connect the SNS pin to the load. Do not float this pin. For fixed-voltage version devices only.
Thermal pad	Pad	Pad	—	Exposed pad of the package. Connect this pad to ground or leave floating. Connect the thermal pad to a large-area ground plane for best thermal performance.

6 Specifications

6.1 Absolute Maximum Ratings

Over operating free-air temperature range (unless otherwise noted)[1]

		MIN	MAX	UNIT
Voltage[2]	V_{IN}	−0.3	18	V
	V_{OUT}[3]	−0.3	V_{IN} + 0.3	
	V_{SNS}[3]	−0.3	V_{IN} + 0.3	
	V_{FB}	−0.3	3	
	V_{EN}	−0.3	18	
Current	Maximum output current	Internally Limited		A
Temperature	Operating junction (T_J)	−50	150	°C
	Storage (T_{STG})	−65	150	

(1)   Stresses beyond those listed under *Absolute Maximum Rating* may cause permanent damage to the device. These are stress ratings only, which do not imply functional operation of the device at these or any other conditions beyond those indicated under *Recommended Operating Condition*. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.
(2)   All voltages with respect to GND.
(3) V_{IN} + 0.3 V or 18 V (whichever is smaller)

6.2 ESD Ratings

			VALUE	UNIT
$V_{(ESD)}$	Electrostatic discharge	Human body model (HBM), per ANSI/ESDA/JEDEC JS-001, all pins[1]	±3000	V
		Charged device model (CDM), per JEDEC specification JESD22-C101, all pins[2]	±1000	

(1)   JEDEC document JEP155 states that 500-V HBM allows safe manufacturing with a standard ESD control process.
(2)   JEDEC document JEP157 states that 250-V CDM allows safe manufacturing with a standard ESD control process.

6.3 Recommended Operating Conditions

over operating free-air temperature range (unless otherwise noted)

		MIN	NOM	MAX	UNIT
V_{IN}	Input voltage	2.5		16	V
V_{EN}	Enable voltage	0		16	V
V_{OUT}	Output voltage	0.8		13.6	V
I_{OUT}	Output current (2.5 V ≤ V_{IN} < 3 V)	0		0.8	A
I_{OUT}	Output current (V_{IN} ≥ 3 V)	0		1	A
C_{OUT}	Output capacitor[1]	1	2.2	220	µF
C_{OUT} ESR	Output capacitor ESR	2		500	mΩ
C_{IN}	Input capacitor		1		µF
C_{FF}	Feed-forward capacitor (optional[2], for adjustable device only)		10		pF
$I_{FB\_DIVIDER}$	Feedback divider current[2] (adjustable device only)	5			µA
T_J	Junction temperature	−40		125	°C

(1)   Effective output capacitance of 0.5 µF minimum required for stability.
(2) C_{FF} required for stability if the feedback divider current < 5 µA. Feedback divider current = V_{OUT} / (R_1 + R_2). See *Feed-Forward Capacitor (C_{FF})* section for details.

6.4 Thermal Information

THERMAL METRIC[1]		TLV767	UNIT
		DRV (WSON)	
		6 PINS	
$R_{\theta JA}$	Junction-to-ambient thermal resistance	77.7	°C/W
$R_{\theta JC(top)}$	Junction-to-case (top) thermal resistance	92.3	°C/W
$R_{\theta JB}$	Junction-to-board thermal resistance	40.8	°C/W
Ψ_{JT}	Junction-to-top characterization parameter	4.3	°C/W
Ψ_{JB}	Junction-to-board characterization parameter	40.8	°C/W
$R_{\theta JC(bot)}$	Junction-to-case (bottom) thermal resistance	18.9	°C/W

(1) For more information about traditional and new thermal metrics, see the Semiconductor and IC Package Thermal Metrics application report.

6.5 Electrical Characteristics

Specified at T_J = –40°C to 125°C, V_{IN} = $V_{OUT(nom)}$ + 1.5 V or V_{IN} = 2.5 V (whichever is greater), FB/SNS tied to OUT, I_{OUT} = 10 mA, V_{EN} = 2 V, C_{IN} = 1.0 µF, C_{OUT} = 1.0 µF (unless otherwise noted). Typical values are at T_J= 25°C.

PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT
V_{OUT}	Nominal output accuracy	T_J = 25°C	–0.5		0.5	%
V_{OUT}	Output accuracy over temperature	V_{IN} ≥ 3.0 V, 1 mA ≤ I_{OUT} ≤ 1 A	–1		1	%
		2.5 V ≤ V_{IN} < 3.0 V, 1 mA ≤ I_{OUT} ≤ 800 mA	–1		1	
V_{FB}	Feedback voltage			0.8		V
V_{REF}	Internal reference (adjustable device)	T_J = 25°C	–0.5		0.5	%
			–1		1	
I_{FB}	Feedback pin current	V_{FB} = 1 V		10	50	nA
$\Delta V_{OUT(\Delta VIN)}$	Line regulation[1]	$V_{OUT(NOM)}$ +1.5 V ≤ V_{IN} ≤ 16 V, I_{OUT} = 10 mA			0.02	%/V
$\Delta V_{OUT(\Delta IOUT)}$	Load regulation	1 mA ≤ I_{OUT} ≤ 1 A, V_{IN} ≥ 3.0 V		0.1	0.5	%/A
		1 mA ≤ I_{OUT} ≤ 800 mA, 2.5 V ≤ V_{IN} < 3.0 V		0.1	0.5	
V_{DO}	Dropout voltage[2]	V_{IN} ≥ 3.0V, I_{OUT} = 1 A		0.9	1.4	V
		2.5 V ≤ V_{IN} < 3.0 V, I_{OUT} = 800 mA		0.8	1.3	
I_{CL}	Output current limit	V_{OUT} = 0.9 x $V_{OUT(NOM)}$, V_{IN} ≥ 3.0V	1.1		1.6	A
		V_{OUT} = 0.9 x $V_{OUT(NOM)}$, 2.5 V ≤ V_{IN} < 3.0 V	0.81		1.6	
I_{SC}	Short-circuit current limit	V_{OUT} = 0 V	150	250	350	mA
I_Q	Quiescent current	I_{OUT} = 0 mA		50	80	µA
		Fixed output devices, I_{OUT} = 0 mA		60	95	
I_{GND}	Ground current	I_{OUT} = 1 A, V_{IN} ≥ 3.0 V		1.5		mA
$I_{SHUTDOWN}$	Shutdown current	V_{EN} ≤ 0.4 V, V_{IN} = 16 V		1.5	3	µA
$V_{EN(HIGH)}$	Enable pin logic high	2.5 V ≤ V_{IN} ≤ 16 V	1.2			V
$V_{EN(LOW)}$	Enable pin logic low	2.5 V ≤ V_{IN} ≤ 16 V			0.4	V
I_{EN}	Enable pullup current	V_{EN} = 0 V		400		nA
$I_{PULLDOWN}$	Output pulldown current	V_{IN} = 16 V, V_{OUT} = 2.5 V		1.2		mA
PSRR	Power-supply rejection ratio	V_{IN} = 3.3 V, V_{OUT} = 1.8 V, I_{OUT} = 300 mA, f = 120 Hz		70		dB
V_n	Output noise voltage	BW = 10 Hz to 100 kHz, V_{IN} = 3.3 V, V_{OUT} = 0.8 V, I_{OUT} = 100 mA		60		µV$_{RMS}$
V_{UVLO+}	UVLO threshold rising	V_{IN} rising		2.2	2.4	V

(1) Line regulation is measured with V_{IN} = $V_{OUT(NOM)}$ + 1.5 V or 2.5 V (whichever is greater)
(2) V_{DO} is measured with V_{IN} = 95% x $V_{OUT(nom)}$ for fixed output devices. V_{DO} is not measured for fixed output devices when V_{OUT} < 2.5 V. For adjustable output device, V_{DO} is measured with V_{FB} = 95% x $V_{FB(nom)}$

Electrical Characteristics (continued)

Specified at T_J = –40°C to 125°C, V_{IN} = $V_{OUT(nom)}$ + 1.5 V or V_{IN} = 2.5 V (whichever is greater), FB/SNS tied to OUT, I_{OUT} = 10 mA, V_{EN} = 2 V, C_{IN} = 1.0 μF, C_{OUT} = 1.0 μF (unless otherwise noted). Typical values are at T_J= 25°C.

PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT
$V_{UVLO(HYS)}$	UVLO hysteresis			130		mV
V_{UVLO-}	UVLO threshold falling	V_{IN} falling	1.9			V
$T_{SD(shutdown)}$	Thermal shutdown temperature	Temperature increasing		180		ºC
$T_{SD(reset)}$	Thermal shutdown reset temperature	Temperature falling		160		ºC

6.6 Typical Characteristics

at operating temperature T_J = 25°C, V_{IN} = $V_{OUT(NOM)}$ + 1.5 V or 2.5 V (whichever is greater), I_{OUT} = 10 mA, V_{EN} = 2.0 V, C_{IN} = 1.0 µF, and C_{OUT} = 1.0 µF (unless otherwise noted)
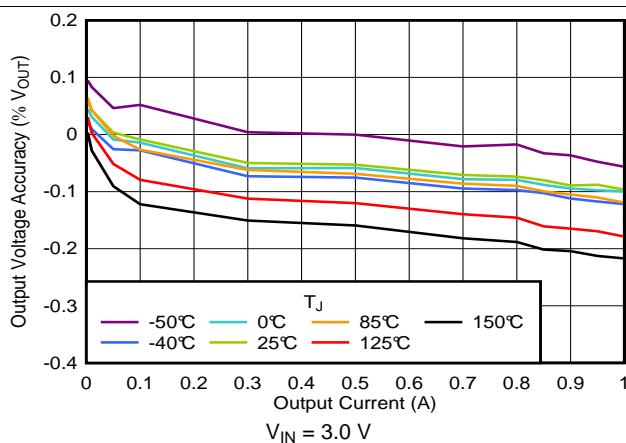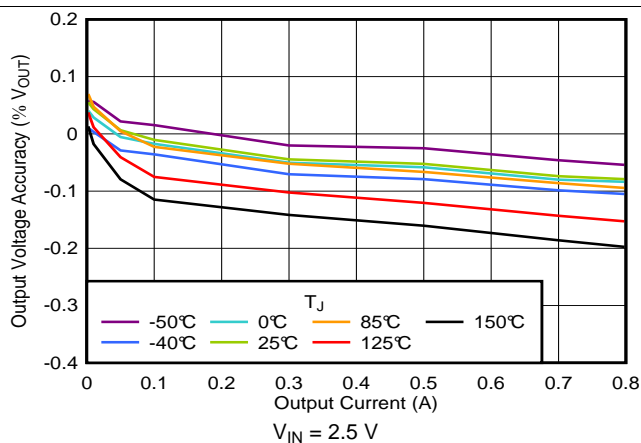
图 1. V_{OUT} Accuracy vs I_{OUT}

图 2. V_{OUT} Accuracy vs I_{OUT}
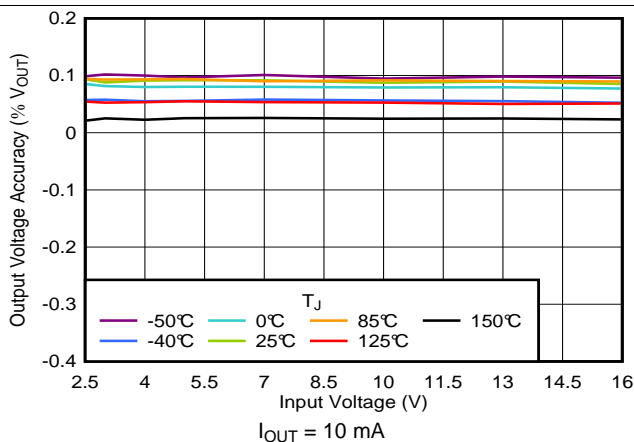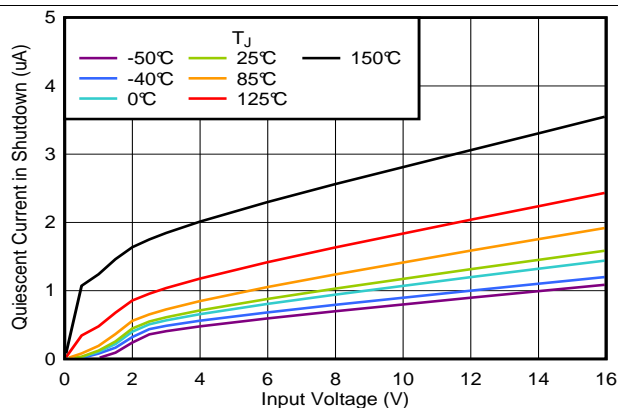
图 3. V_{OUT} Accuracy vs V_{IN}

图 4. $I_{SHUTDOWN}$ vs V_{IN}
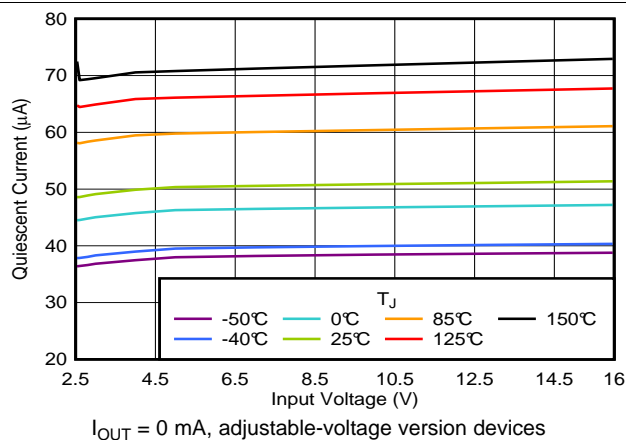
图 5. I_Q vs V_{IN}

图 6. I_Q vs Temperature
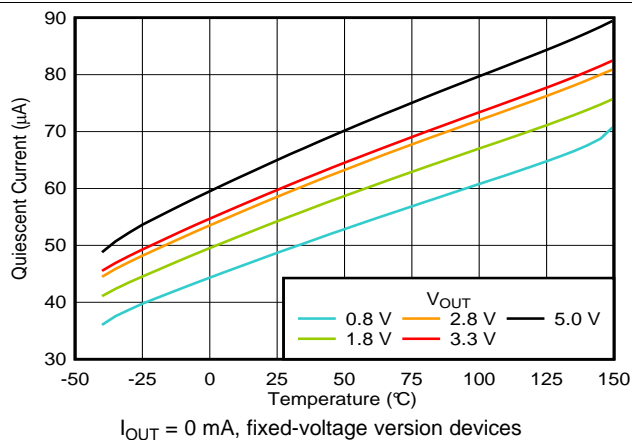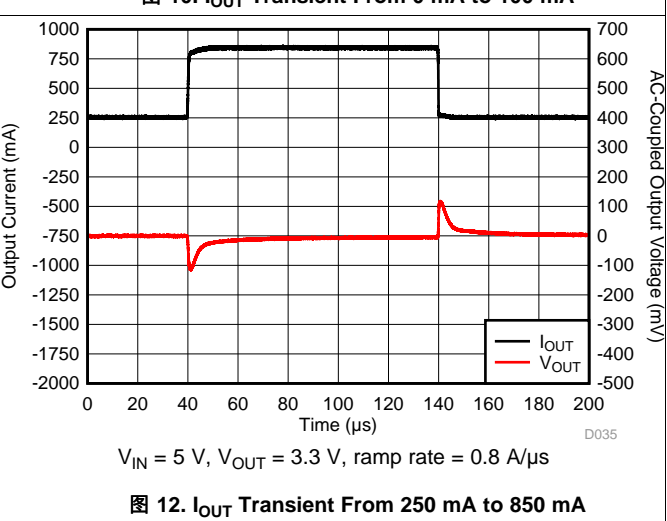
Typical Characteristics (接下页)

at operating temperature T_J = 25°C, V_{IN} = $V_{OUT(NOM)}$ + 1.5 V or 2.5 V (whichever is greater), I_{OUT} = 10 mA, V_{EN} = 2.0 V, C_{IN} = 1.0 µF, and C_{OUT} = 1.0 µF (unless otherwise noted)

V_{IN} = 3.0 V

图 7. I_{GND} vs I_{OUT}

V_{IN} = 2.5 V

图 8. I_{GND} vs I_{OUT}

I_{OUT} = 0 mA

图 9. I_Q Increase Below Minimum V_{IN}

V_{IN} = 5 V, V_{OUT} = 3.3 V, C_{FF} = 10 pF, ramp rate = 0.4 A/µs

图 10. I_{OUT} Transient From 0 mA to 100 mA

V_{IN} = 5 V, V_{OUT} = 3.3 V, C_{FF} = 10 pF, ramp rate = 0.5 A/µs

图 11. I_{OUT} Transient From 1 mA to 1 A

V_{IN} = 5 V, V_{OUT} = 3.3 V, ramp rate = 0.8 A/µs

图 12. I_{OUT} Transient From 250 mA to 850 mA

Typical Characteristics (接下页)

at operating temperature T_J = 25°C, V_{IN} = $V_{OUT(NOM)}$ + 1.5 V or 2.5 V (whichever is greater), I_{OUT} = 10 mA, V_{EN} = 2.0 V, C_{IN} = 1.0 μF, and C_{OUT} = 1.0 μF (unless otherwise noted)

V_{OUT} = 3.3 V, I_{OUT} = 1 A, V_{IN} ramp rate = 0.6 V/μs

图 13. V_{IN} Transient in Dropout From 4 V to 13 V

V_{OUT} = 3.3 V, I_{OUT} = 33 μA, V_{IN} ramp rate = 1.6 V/μs
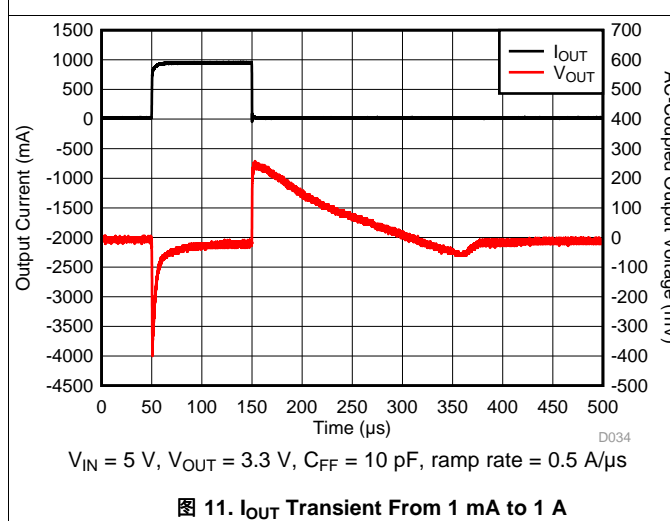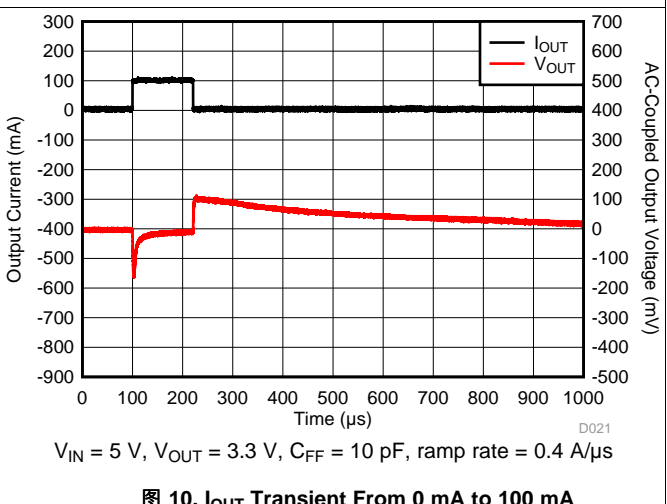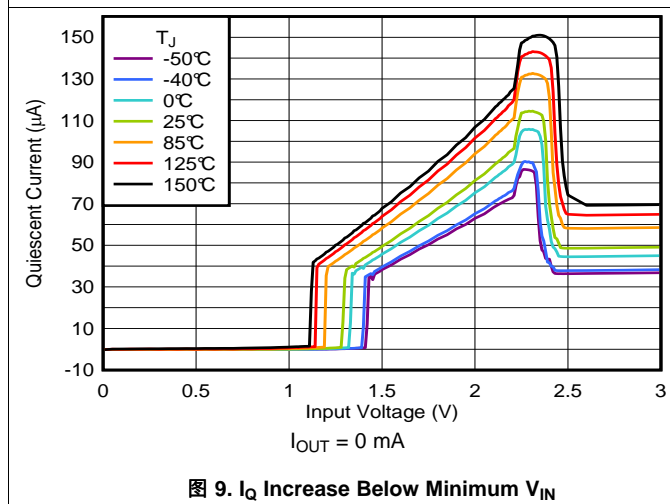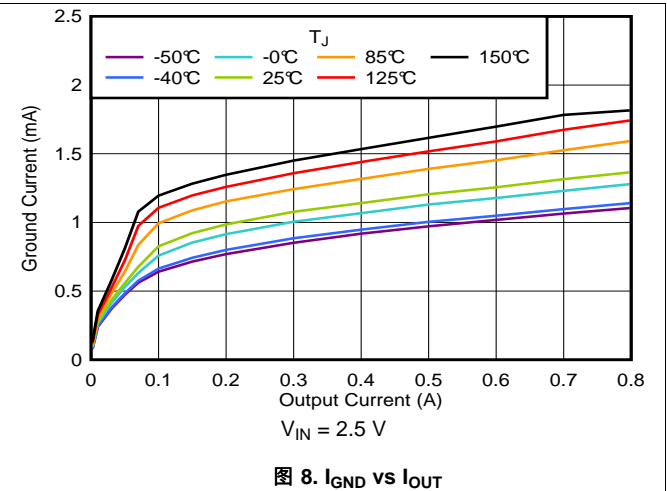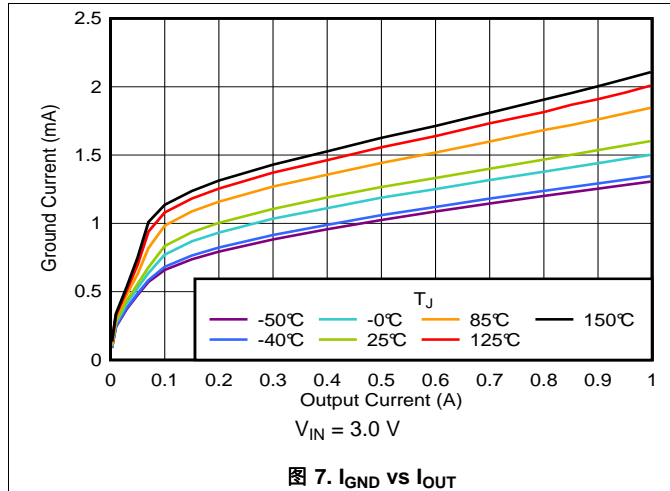
图 14. V_{IN} Transient From 5 V to 16 V

I_{OUT} = 1.0 A

图 15. V_{DO} vs V_{IN}

I_{OUT} = 0.8 A

图 16. V_{DO} vs V_{IN}

V_{IN} = 3.0 V

图 17. V_{DO} vs I_{OUT}

V_{IN} = 2.5 V
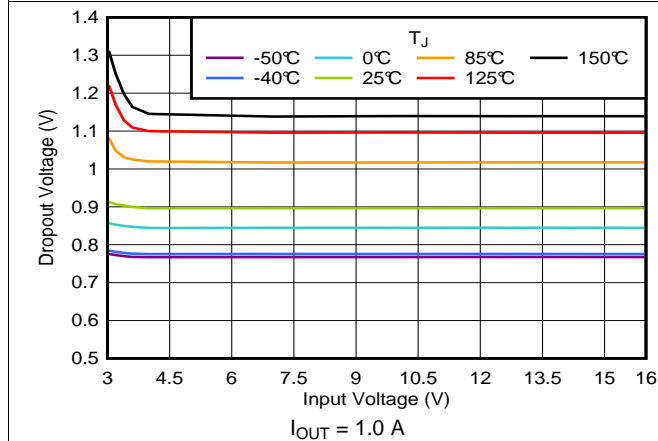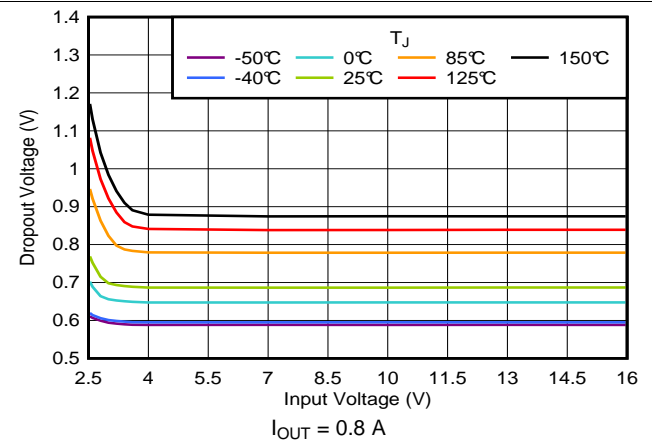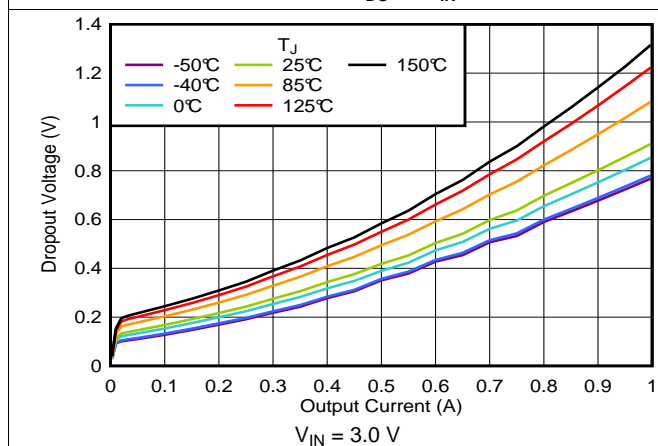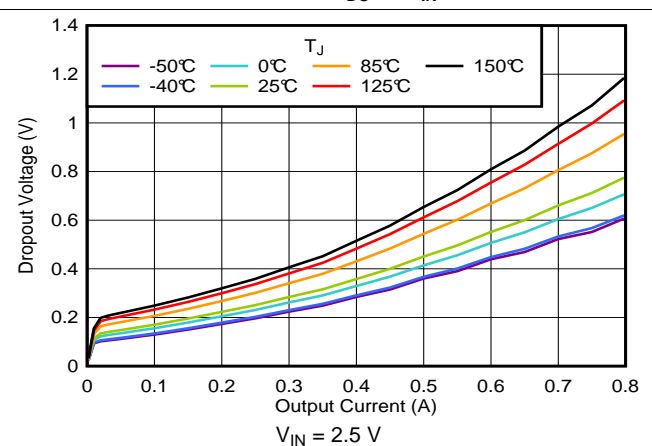
图 18. V_{DO} vs I_{OUT}

Typical Characteristics (接下页)

at operating temperature T_J = 25°C, V_{IN} = $V_{OUT(NOM)}$ + 1.5 V or 2.5 V (whichever is greater), I_{OUT} = 10 mA, V_{EN} = 2.0 V, C_{IN} = 1.0 µF, and C_{OUT} = 1.0 µF (unless otherwise noted)

V_{IN} = 3.0 V

图 19. Foldback Current Limit vs Temperature

V_{IN} = 2.5 V

图 20. Foldback Current Limit vs Temperature

V_{OUT} = 3.3 V

图 21. Startup With Separate V_{EN} and V_{IN}

Enable pulled up internally, V_{OUT} = 0.8 V

图 22. Startup With V_{EN} Floating

V_{IN} = 2.5 V

图 23. V_{EN} Thresholds vs Temperature

V_{IN} = 16 V

图 24. V_{EN} Thresholds vs Temperature

Typical Characteristics (接下页)

at operating temperature T_J = 25°C, V_{IN} = $V_{OUT(NOM)}$ + 1.5 V or 2.5 V (whichever is greater), I_{OUT} = 10 mA, V_{EN} = 2.0 V, C_{IN} = 1.0 µF, and C_{OUT} = 1.0 µF (unless otherwise noted)

图 25. UVLO Thresholds vs Temperature

V_{OUT} = 1.8 V, V_{IN} = 3.3 V, C_{FF} = 1 nF

图 26. PSRR vs I_{OUT}

V_{OUT} = 1.8 V, I_{OUT} = 0.55 A, C_{FF} = 1 nF

图 27. PSRR vs V_{IN}

V_{OUT} = 3.3 V, V_{IN} = 4.8 V, I_{OUT} = 0.33 A

图 28. PSRR vs C_{FF}

C_{FF} = 0 nF, I_{OUT} = 0.1 A, RMS noise BW = 10 Hz to 100 kHz

图 29. Output Noise (V_n) vs V_{OUT}

V_{EN} = 0 V

图 30. I_{EN} vs V_{IN}

Typical Characteristics (接下页)

at operating temperature T_J = 25°C, V_{IN} = $V_{OUT(NOM)}$ + 1.5 V or 2.5 V (whichever is greater), I_{OUT} = 10 mA, V_{EN} = 2.0 V, C_{IN} = 1.0 µF, and C_{OUT} = 1.0 µF (unless otherwise noted)

V_{OUT} = 2.5 V
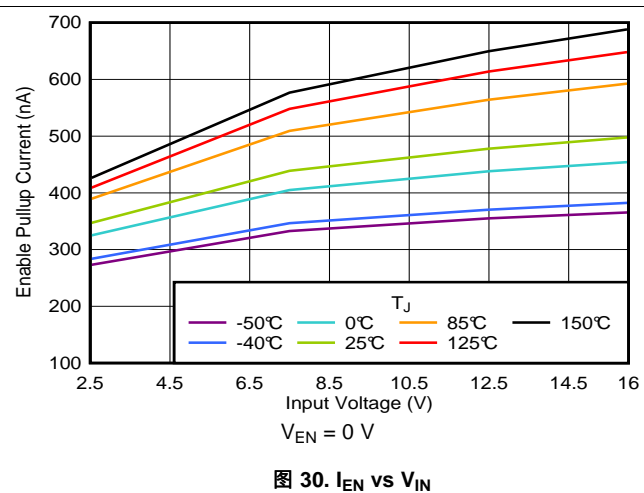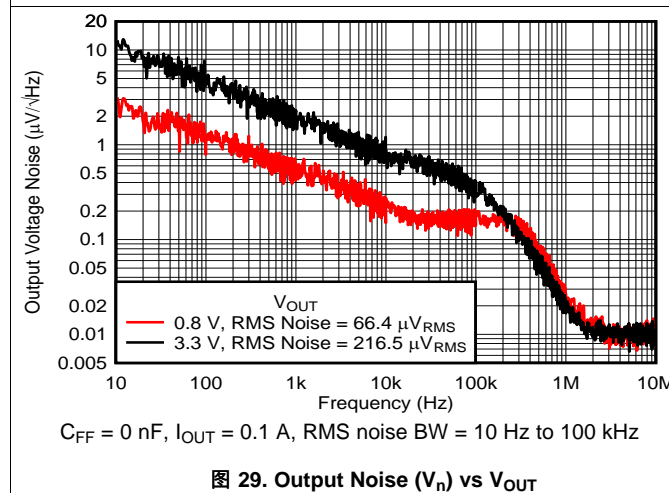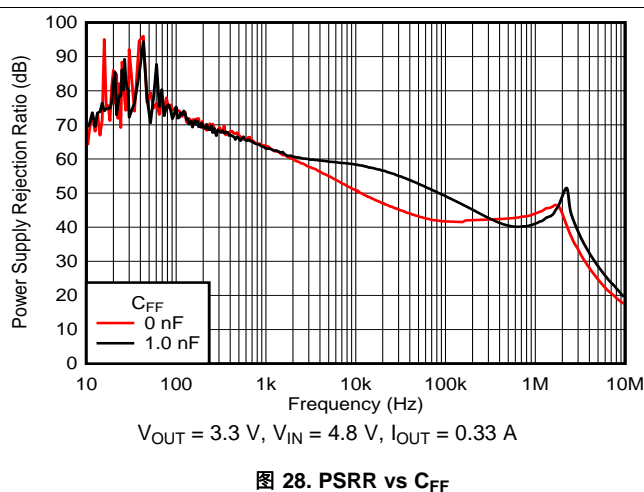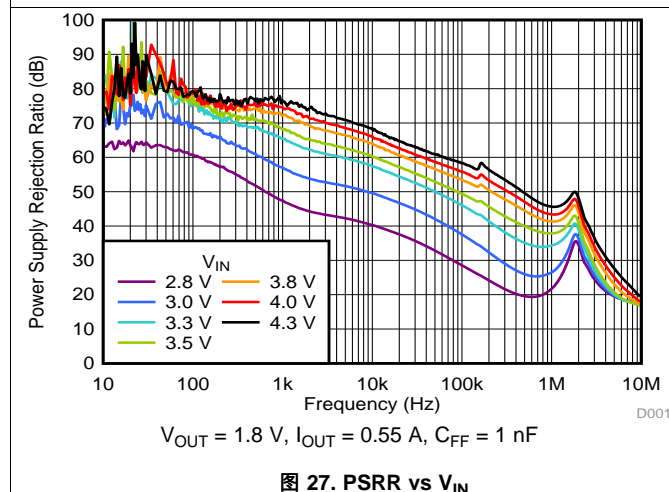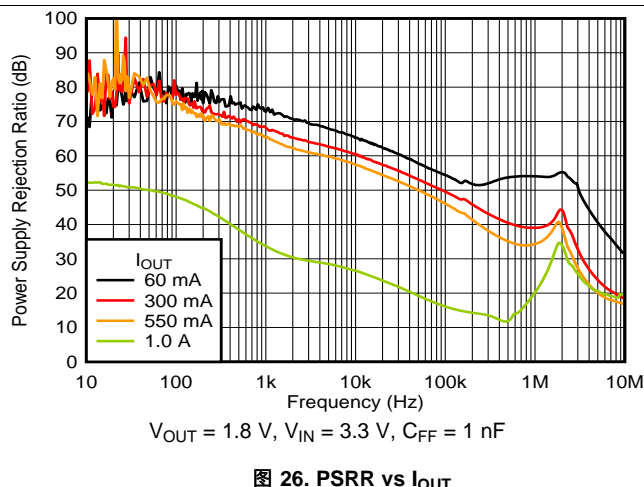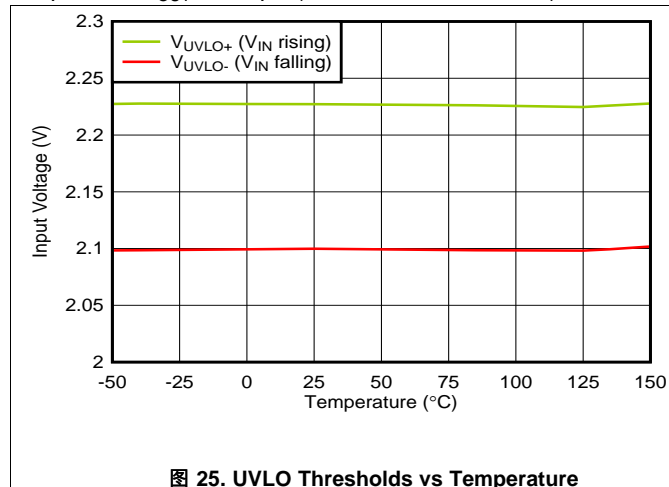
图 31. $I_{PULLDOWN}$ vs V_{IN}

V_{FB} = 1.0 V

图 32. I_{FB} vs Temperature

V_{OUT} = 3.3 V, I_{OUT} = 33 µA
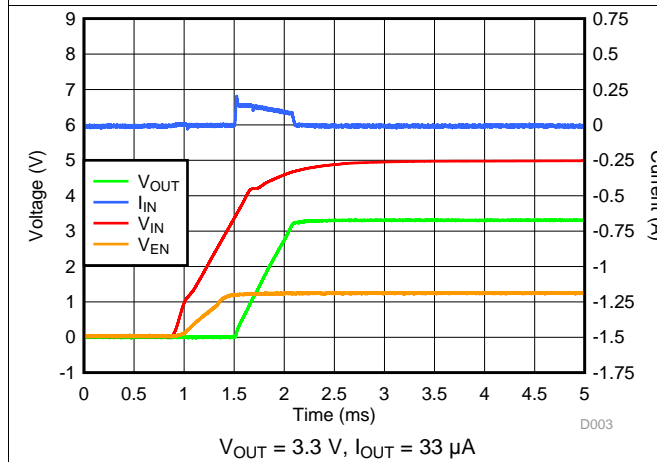
图 33. Startup Inrush Current With C_{OUT} = 22 µF

V_{OUT} = 3.3 V, I_{OUT} = 33 µA
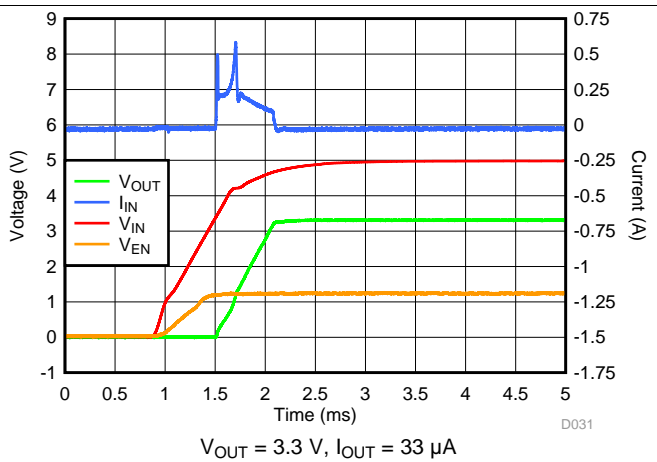
图 34. Startup Inrush Current With C_{OUT} = 47 µF

7 Detailed Description

7.1 Overview

The TLV767 is a low quiescent current, high PSRR linear regulator capable of handling up to 1 A of load current. Unlike typical high current linear regulators, the TLV767 consumes significantly less quiescent current. This device is ideal for high current applications that require very sensitive power-supply rails.

This device features integrated foldback current limit, thermal shutdown, output enable, internal output pulldown and undervoltage lockout (UVLO). This device delivers excellent line and load transient performance. This device is low noise and exhibits a very good PSRR. The operating ambient temperature range of the device is −40°C to 125°C.

7.2 Functional Block Diagrams
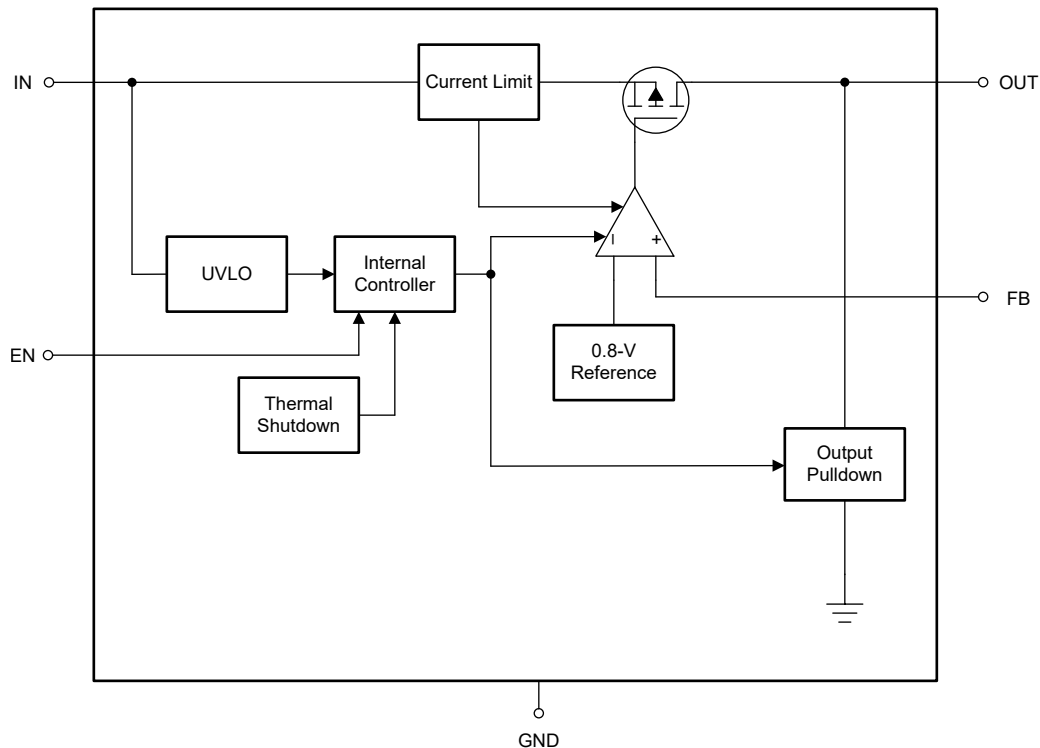
图 35. **Adjustable Version Block Diagram**

Functional Block Diagrams (continued)
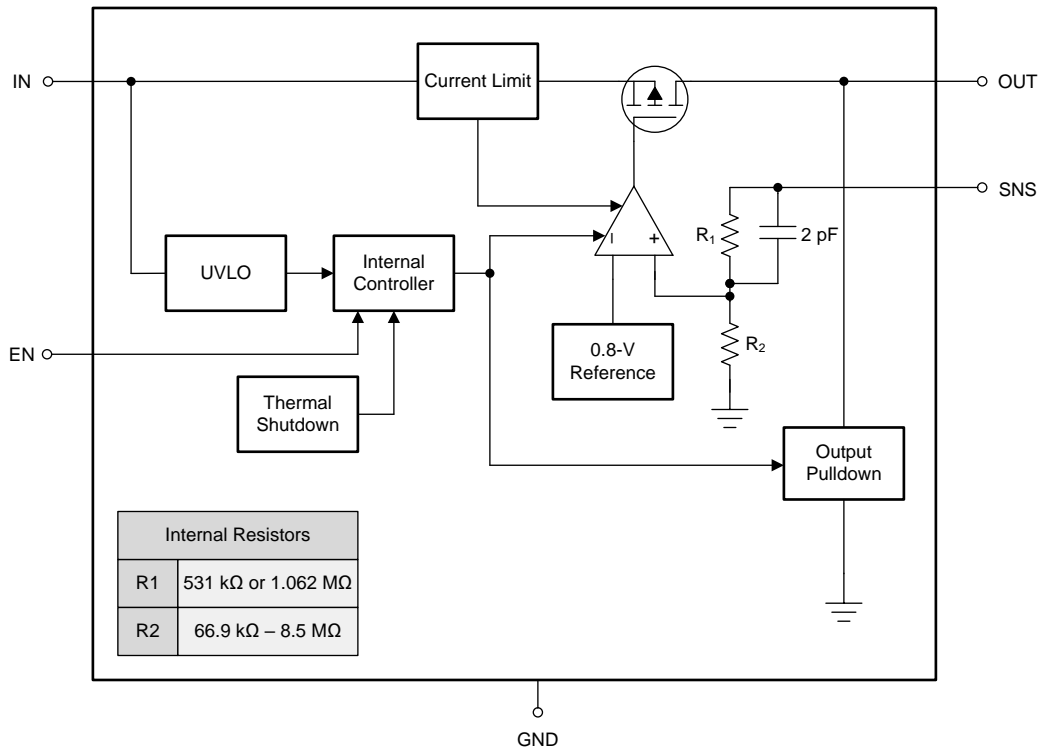
图 36. Fixed Version Block Diagram

7.3 Feature Description

7.3.1 Output Enable

The enable pin for the device is an active-high pin. The output voltage is enabled when the voltage of the enable pin is greater than the high-level input voltage of the EN pin and disabled with the enable pin voltage is less than the low-level input voltage of the EN pin. If independent control of the output voltage is not needed, connect the enable pin to the input of the device.

This device has an internal pullup current on the EN pin. The EN pin can be left floating to enable the device.

The device has an internal pulldown circuit that activates when the device is disabled to actively discharge the output voltage.

7.3.2 Dropout Voltage

Dropout voltage (V_{DO}) is defined as the input voltage minus the output voltage ($V_{IN} - V_{OUT}$) at the rated output current (I_{RATED}), where the pass transistor is fully on. I_{RATED} is the maximum I_{OUT} listed in the *Recommended Operating Conditions* table. The pass transistor is in the ohmic or triode region of operation, and acts as a switch. The dropout voltage indirectly specifies a minimum input voltage greater than the nominal programmed output voltage at which the output voltage is expected to stay in regulation. If the input voltage falls to less than the nominal output regulation, then the output voltage falls as well.

For a CMOS regulator, the dropout voltage is determined by the drain-source on-state resistance ($R_{DS(ON)}$) of the pass transistor. Therefore, if the linear regulator operates at less than the rated current, the dropout voltage for that current scales accordingly. Use Equation 1 to calculate the $R_{DS(ON)}$ of the device.

$$R_{DS(ON)} = \frac{V_{DO}}{I_{RATED}}$$

(1)

Feature Description (continued)

7.3.3 Foldback Current Limit

The device has an internal current limit circuit that protects the regulator during transient high-load current faults or shorting events. The current limit is a hybrid brickwall-foldback scheme. The current limit transitions from a brickwall scheme to a foldback scheme at the foldback voltage ($V_{FOLDBACK}$). In a high-load current fault with the output voltage above $V_{FOLDBACK}$, the brickwall scheme limits the output current to the current limit (I_{CL}). When the voltage drops below $V_{FOLDBACK}$, a foldback current limit activates that scales back the current as the output voltage approaches GND. When the output is shorted, the device supplies a typical current called the short-circuit current limit (I_{SC}). I_{CL} and I_{SC} are listed in the *Electrical Characteristics* table.

For this device, $V_{FOLDBACK} = 50\% \times V_{OUT(nom)}$.

The output voltage is not regulated when the device is in current limit. When a current limit event occurs, the device begins to heat up because of the increase in power dissipation. When the device is in brickwall current limit, the pass transistor dissipates power [$(V_{IN} - V_{OUT}) \times I_{CL}$]. When the device output is shorted and the output is below $V_{FOLDBACK}$, the pass transistor dissipates power [$(V_{IN} - V_{OUT}) \times I_{SC}$]. If thermal shutdown is triggered, the device turns off. After the device cools down, the internal thermal shutdown circuit turns the device back on. If the output current fault condition continues, the device cycles between current limit and thermal shutdown. For more information on current limits, see the *Know Your Limits* application report.

Figure 37 shows a diagram of the foldback current limit.
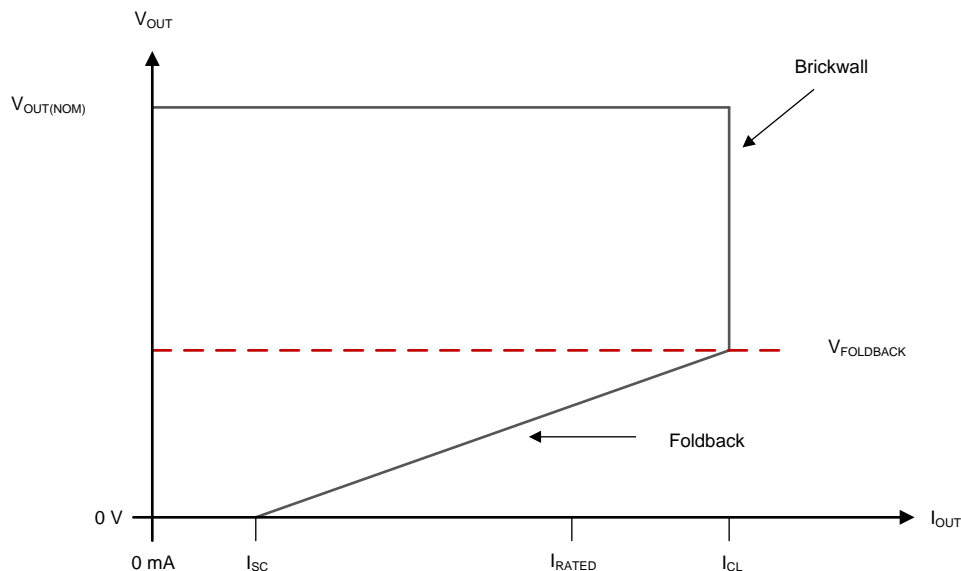
Figure 37. Foldback Current Limit

7.3.4 Undervoltage Lockout (UVLO)

The device has an independent undervoltage lockout (UVLO) circuit that monitors the input voltage, allowing a controlled and consistent turn on and off of the output voltage. To prevent the device from turning off if the input drops during turn on, the UVLO has hysteresis as specified in the *Electrical Characteristics* table.

7.3.5 Output Pulldown

The device has an output pulldown circuit. V_{OUT} pulldown sink to ground capability is listed in the *Electrical Characteristics* table. The output pulldown activates under the following conditions:
- Device disabled
- $1.0\ V < V_{IN} < V_{UVLO}$

Feature Description (continued)

The output pulldown current for this device is 1.2 mA typical, as listed in the *Electrical Characteristics* table.

Do not rely on the output pulldown circuit for discharging a large amount of output capacitance after the input supply has collapsed because reverse current can flow from the output to the input. This reverse current flow can cause damage to the device. See the *Reverse Current* section for more details.

7.3.6 Thermal Shutdown

The device contains a thermal shutdown protection circuit to disable the device when the junction temperature (T_J) of the pass transistor rises to $T_{SD(shutdown)}$ (typical). Thermal shutdown hysteresis assures that the device resets (turns on) when the temperature falls to $T_{SD(reset)}$ (typical).

The thermal time-constant of the semiconductor die is fairly short, thus the device may cycle on and off when thermal shutdown is reached until power dissipation is reduced. Power dissipation during startup can be high from large $V_{IN} - V_{OUT}$ voltage drops across the device or from high inrush currents charging large output capacitors. Under some conditions, the thermal shutdown protection disables the device before startup completes.

For reliable operation, limit the junction temperature to the maximum listed in the *Recommended Operating Conditions* table. Operation above this maximum temperature causes the device to exceed its operational specifications. Although the internal protection circuitry of the device is designed to protect against thermal overall conditions, this circuitry is not intended to replace proper heat sinking. Continuously running the device into thermal shutdown or above the maximum recommended junction temperature reduces long-term reliability.

7.4 Device Functional Modes

7.4.1 Device Functional Mode Comparison

The *Device Functional Mode Comparison* table shows the conditions that lead to the different modes of operation. See the *Electrical Characteristics* table for parameter values.

Table 1. Device Functional Mode Comparison

OPERATING MODE	PARAMETER			
	V_{IN}	V_{EN}	I_{OUT}	T_J
Normal operation	$V_{IN} > V_{OUT(nom)} + V_{DO}$ and $V_{IN} > V_{IN(min)}$	$V_{EN} > V_{EN(HI)}$	$I_{OUT} < I_{OUT(max)}$	$T_J < T_{SD(shutdown)}$
Dropout operation	$V_{IN(min)} < V_{IN} < V_{OUT(nom)} + V_{DO}$	$V_{EN} > V_{EN(HI)}$	$I_{OUT} < I_{OUT(max)}$	$T_J < T_{SD(shutdown)}$
Disabled (any true condition disables the device)	$V_{IN} < V_{UVLO}$	$V_{EN} < V_{EN(LOW)}$	Not applicable	$T_J > T_{SD(shutdown)}$

7.4.2 Normal Operation

The device regulates to the nominal output voltage when the following conditions are met:
- The input voltage is greater than the nominal output voltage plus the dropout voltage ($V_{OUT(nom)} + V_{DO}$)
- The output current is less than the current limit ($I_{OUT} < I_{CL}$)
- The device junction temperature is less than the thermal shutdown temperature ($T_J < T_{SD}$)
- The enable voltage has previously exceeded the enable rising threshold voltage and has not yet decreased to less than the enable falling threshold

7.4.3 Dropout Operation

If the input voltage is lower than the nominal output voltage plus the specified dropout voltage, but all other conditions are met for normal operation, the device operates in dropout mode. In this mode, the output voltage tracks the input voltage. During this mode, the transient performance of the device becomes significantly degraded because the pass transistor is in the ohmic or triode region, and acts as a switch. Line or load transients in dropout can result in large output-voltage deviations.

When the device is in a steady dropout state (defined as when the device is in dropout, $V_{IN} < V_{OUT(NOM)} + V_{DO}$, directly after being in a normal regulation state, but *not* during startup), the pass transistor is driven into the ohmic or triode region. When the input voltage returns to a value greater than or equal to the nominal output voltage plus the dropout voltage ($V_{OUT(NOM)} + V_{DO}$), the output voltage can overshoot for a short period of time while the device pulls the pass transistor back into the linear region.

7.4.4 Disabled

The output of the device can be shutdown by forcing the voltage of the enable pin to less than the maximum EN pin low-level input voltage (see the *Electrical Characteristics* table). When disabled, the pass transistor is turned off, internal circuits are shutdown, and the output voltage is actively discharged to ground by an internal discharge circuit from the output to ground.

8 Application and Implementation

> 注
>
> Information in the following applications sections is not part of the TI component specification, and TI does not warrant its accuracy or completeness. TI's customers are responsible for determining suitability of components for their purposes. Customers should validate and test their design implementation to confirm system functionality.

8.1 Application Information

8.1.1 Adjustable Device Feedback Resistors

The adjustable-version device requires external feedback divider resistors to set the output voltage. V_{OUT} is set using the feedback divider resistors, R_1 and R_2, according to the following equation:

$$V_{OUT} = V_{FB} \times (1 + R_1 / R_2) \tag{2}$$

To ignore the FB pin current error term in the V_{OUT} equation, set the feedback divider current to 100x the FB pin current listed in the *Electrical Characteristics* table. This setting provides the maximum feedback divider series resistance, as shown in the following equation:

$$R_1 + R_2 \leq V_{OUT} / (I_{FB} \times 100) \tag{3}$$

8.1.2 Recommended Capacitor Types

The device is designed to be stable using low equivalent series resistance (ESR) ceramic capacitors at the input and output. Multilayer ceramic capacitors have become the industry standard for these types of applications and are recommended, but must be used with good judgment. Ceramic capacitors that employ X7R-, X5R-, and C0G-rated dielectric materials provide relatively good capacitive stability across temperature, whereas the use of Y5V-rated capacitors is discouraged because of large variations in capacitance.

Regardless of the ceramic capacitor type selected, the effective capacitance varies with operating voltage and temperature. As a rule of thumb, expect the effective capacitance to decrease by as much as 50%. The input and output capacitors recommended in the *Recommended Operating Conditions* table account for an effective capacitance of approximately 50% of the nominal value.

8.1.3 Input and Output Capacitor Requirements

Although an input capacitor is not required for stability, good analog design practice is to connect a capacitor from IN to GND. This capacitor counteracts reactive input sources and improves transient response, input ripple, and PSRR. An input capacitor is recommended if the source impedance is more than 0.5 Ω. A higher value capacitor may be necessary if large, fast rise-time load or line transients are anticipated or if the device is located several inches from the input power source.

Dynamic performance of the device is improved with the use of an output capacitor. Use an output capacitor within the range specified in the *Recommended Operating Conditions* table for stability.

Application Information (continued)

8.1.4 Reverse Current

Excessive reverse current can damage this device. Reverse current flows through the intrinsic body diode of the pass transistor instead of the normal conducting channel. At high magnitudes, this current flow degrades the long-term reliability of the device.

Conditions where reverse current can occur are outlined in this section, all of which can exceed the absolute maximum rating of $V_{OUT} \leq V_{IN} + 0.3$ V.

- If the device has a large C_{OUT} and the input supply collapses with little or no load current
- The output is biased when the input supply is not established
- The output is biased above the input supply

If reverse current flow is expected in the application, external protection is recommended to protect the device. Reverse current is not limited in the device, so external limiting is required if extended reverse voltage operation is anticipated.

Figure 38 shows one approach for protecting the device.
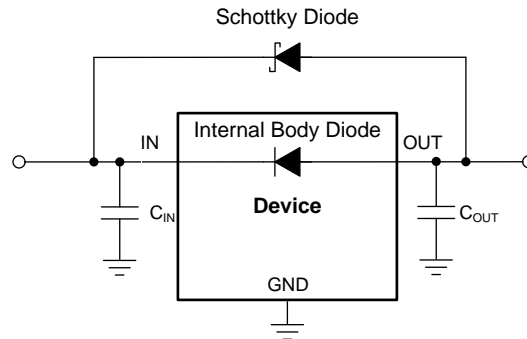
Figure 38. Example Circuit for Reverse Current Protection Using a Schottky Diode

8.1.5 Feed-Forward Capacitor (C_{FF})

For the adjustable-voltage version device, a feed-forward capacitor (C_{FF}) can be connected from the OUT pin to the FB pin. C_{FF} improves transient, noise, and PSRR performance, but is not required for regulator stability. Recommended C_{FF} values are listed in the *Recommended Operating Conditions* table. A higher capacitance C_{FF} can be used; however, the startup time increases. For a detailed description of C_{FF} tradeoffs, see the *Pros and Cons of Using a Feedforward Capacitor with a Low-Dropout Regulator* application report.

C_{FF} and R_1 form a zero in the loop gain at frequency f_Z, while C_{FF}, R_1, and R_2 form a pole in the loop gain at frequency f_P. C_{FF} zero and pole frequencies can be calculated from the following equations:

$$f_Z = 1 / (2 \times \pi \times C_{FF} \times R_1) \tag{4}$$
$$f_P = 1 / (2 \times \pi \times C_{FF} \times (R_1 \| R_2)) \tag{5}$$

$C_{FF} \geq 10$ pF is required for stability if the feedback divider current is less than 5 µA. 公式 6 calculates the feedback divider current.

$$I_{FB\_Divider} = V_{OUT} / (R_1 + R_2) \tag{6}$$

To avoid startup time increases from C_{FF}, limit the product $C_{FF} \times R_1 < 50$ µs.

For an output voltage of 0.8 V with the FB pin tied to the OUT pin, no C_{FF} is used.

Application Information (continued)

8.1.6 Power Dissipation (P$_D$)

Circuit reliability requires consideration of the device power dissipation, location of the circuit on the printed circuit board (PCB), and correct sizing of the thermal plane. The PCB area around the regulator must have few or no other heat-generating devices that cause added thermal stress.

To first-order approximation, power dissipation in the regulator depends on the input-to-output voltage difference and load conditions. Equation 7 calculates power dissipation (P$_D$).

$$P_D = (V_{IN} - V_{OUT}) \times I_{OUT} \tag{7}$$

NOTE

Power dissipation can be minimized, and therefore greater efficiency can be achieved, by correct selection of the system voltage rails. For the lowest power dissipation use the minimum input voltage required for correct output regulation.

For devices with a thermal pad, the primary heat conduction path for the device package is through the thermal pad to the PCB. Solder the thermal pad to a copper pad area under the device. This pad area must contain an array of plated vias that conduct heat to additional copper planes for increased heat dissipation.

The maximum power dissipation determines the maximum allowable ambient temperature (T$_A$) for the device. According to Equation 8, power dissipation and junction temperature are most often related by the junction-to-ambient thermal resistance (R$_{\theta JA}$) of the combined PCB and device package and the temperature of the ambient air (T$_A$).

$$T_J = T_A + (R_{\theta JA} \times P_D) \tag{8}$$

Thermal resistance (R$_{\theta JA}$) is highly dependent on the heat-spreading capability built into the particular PCB design, and therefore varies according to the total copper area, copper weight, and location of the planes. The junction-to-ambient thermal resistance listed in the *Thermal Information* table is determined by the JEDEC standard PCB and copper-spreading area, and is used as a relative measure of package thermal performance.

8.1.7 Estimating Junction Temperature

The JEDEC standard now recommends the use of psi (Ψ) thermal metrics to estimate the junction temperatures of the linear regulator when in-circuit on a typical PCB board application. These metrics are not thermal resistance parameters and instead offer a practical and relative way to estimate junction temperature. These psi metrics are determined to be significantly independent of the copper area available for heat-spreading. The *Thermal Information* table lists the primary thermal metrics, which are the junction-to-top characterization parameter (ψ_{JT}) and junction-to-board characterization parameter (ψ_{JB}). These parameters provide two methods for calculating the junction temperature (T$_J$). As described in , use the junction-to-top characterization parameter (ψ_{JT}) with the temperature at the center-top of device package (T$_T$) to calculate the junction temperature. As described in , use the junction-to-board characterization parameter (ψ_{JB}) with the PCB surface temperature 1 mm from the device package (T$_B$) to calculate the junction temperature.

$$T_J = T_T + \psi_{JT} \times P_D$$

where:

- P$_D$ is the dissipated power
- T$_T$ is the temperature at the center-top of the device package $\tag{9}$

$$T_J = T_B + \psi_{JB} \times P_D$$

where

- T$_B$ is the PCB surface temperature measured 1 mm from the device package and centered on the package edge $\tag{10}$

For detailed information on the thermal metrics and how to use them, see the *Semiconductor and IC Package Thermal Metrics* application report.

8.2 Typical Application

This section discusses implementing this device for a typical application. 图 39 shows the application circuit.
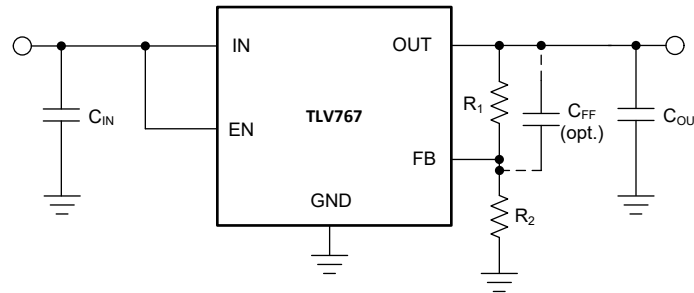
图 39. Typical Application Circuit

8.2.1 Design Requirements

表 2 summarizes the design requirements for this application.

表 2. Design Parameters

PARAMETER	DESIGN REQUIREMENT
Input voltage	5 V
Output voltage	3.3 V
Output current	100 mA

8.2.2 Detailed Design Procedure

8.2.2.1 Transient Response

As with any regulator, increasing the size of the output capacitor reduces overshoot and undershoot magnitude. If load transients are expected with ramp rates greater than 0.5 A/μs, use a 2.2-μF or larger output capacitor.

8.2.3 Choose Feedback Resistors

For this design example, V_{OUT} is set to 3.3 V. The following equations set the feedback divider resistors for the desired output voltage:

$$V_{OUT} = V_{FB} \times (1 + R_1 / R_2) \tag{11}$$

$$R_1 + R_2 \leq V_{OUT} / (I_{FB} \times 100) \tag{12}$$

For improved output accuracy, use Equation 12 and I_{FB} = 50 nA as listed in the *Electrical Characteristics* table to calculate the upper limit for series feedback resistance ($R_1 + R_2 \leq 660$ kΩ).

The control-loop error amplifier drives the FB pin to the same voltage as the internal reference (V_{FB} = 0.8 V, as listed in the *Electrical Characteristics* table). Use Equation 11 to determine the ratio of R_1 / R_2 = 3.125. Use this ratio and solve Equation 12 for R_2. Now calculate the upper limit for $R_2 \leq 160$ kΩ. Select a standard value resistor for R_2 = 160 kΩ.

Reference Equation 11 and solve for R_1:

$$R_1 = (V_{OUT} / V_{FB} - 1) \times R_2 \tag{13}$$

From 公式 13, R_1 = 500 kΩ can be determined. Select a standard value resistor for R_1 = 499 kΩ. V_{OUT} = 3.3 V (as determined by Equation 11).

8.2.4 Application Curves

V_{IN} = 5 V, V_{OUT} = 3.3 V, C_{OUT} = 1 μF, C_{FF} = 10 pF

图 40. Load Transient Response, I_{OUT} 0 mA to 100 mA

V_{IN} = 5 V, V_{OUT} = 3.3 V, C_{OUT} = 1 μF, C_{FF} = 0 pF

图 41. PSRR Performance
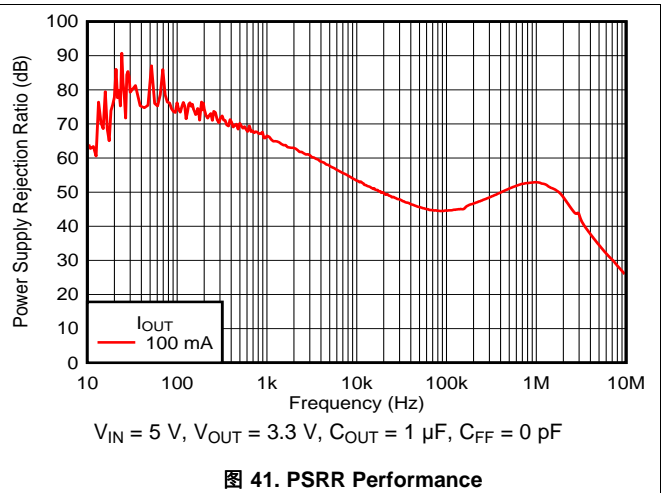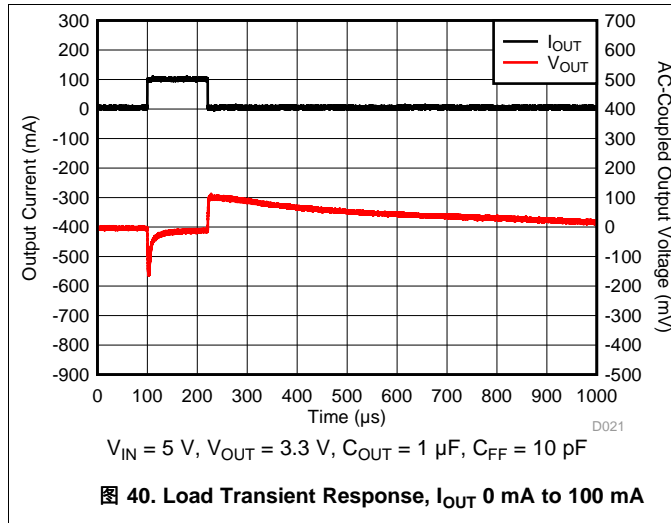
9 Power Supply Recommendations

This device is designed to operate from an input supply voltage range of 2.5 V to 16 V. To ensure that the output voltage is well regulated and dynamic performance is optimum, the input supply must be at least $V_{OUT(nom)}$ + 1.5 V. For 1-A output current operation, the input supply must be 3 V or greater. Connect a low output impedance power supply directly to the input pin of the TLV767.

10 Layout

10.1 Layout Guidelines

- Place input and output capacitors as close to the device as possible
- Use copper planes for device connections to IN, OUT, and GND pins to optimize thermal performance
- Place thermal vias around the device to distribute heat

10.2 Layout Examples

● Represents via used for application-specific connections
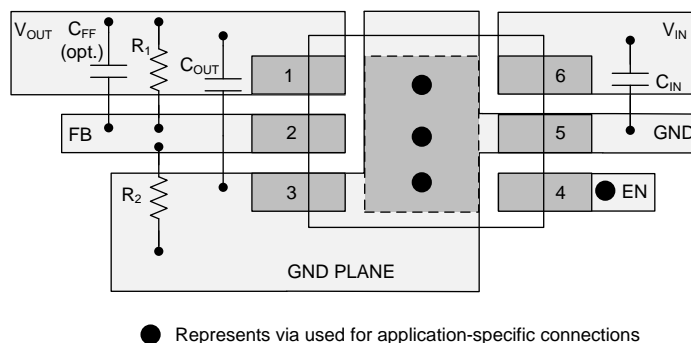
图 42. Layout Example for the Adjustable Version

● Represents via used for application-specific connections
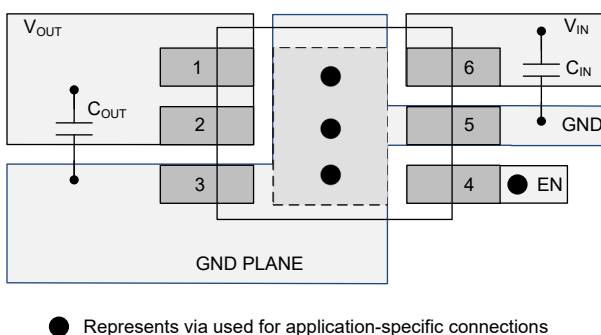
图 43. Layout Example for the Fixed Version

11 器件和文档支持

11.1 器件支持

11.1.1 器件命名规则

表 **3.** 提供的选项[(1)]

产品	V_{OUT}
TLV767**xx(x)yyyz**	**xx(x)** 为标称输出电压。对于分辨率为 100mV 的输出电压，订购编号中使用两位数字；否则，使用三位数字（例如，33 = 3.3V；125 = 1.25V）。01 表示可调节输出版本。 **yyy** 是封装符号。 **z** 是封装数量。R 表示大数量卷带，T 表示小数量卷带。

(1)   要获得最新的封装和订货信息，请参阅本文档末尾的封装选项附录，或者访问www.ti.com.cn上的器件产品文件夹。

11.2 文档支持

11.2.1 相关文档

请参阅如下相关文档：

- 德州仪器 (TI)，*《TLV767EVM-014 评估模块》*用户指南
- 德州仪器 (TI)，*《使用前馈电容器和低压降稳压器的优缺点》*应用报告
- 德州仪器 (TI)，*《了解限制》*应用报告
- 德州仪器 (TI)，*《通用低压降 (LDO) 线性稳压器 MultiPkgLDOEVM-823 评估模块》*用户指南

11.3 接收文档更新通知

要接收文档更新通知，请导航至 TI.com.cn 上的器件产品文件夹。单击右上角的*通知我* 进行注册，即可每周接收产品信息更改摘要。有关更改的详细信息，请查看任何已修订文档中包含的修订历史记录。

11.4 社区资源

下列链接提供到 TI 社区资源的连接。链接的内容由各个分销商"按照原样"提供。这些内容并不构成 TI 技术规范，并且不一定反映 TI 的观点；请参阅 TI 的 *《使用条款》*。

TI E2E™ Online Community *TI's Engineer-to-Engineer (E2E) Community.* Created to foster collaboration among engineers. At e2e.ti.com, you can ask questions, share knowledge, explore ideas and help solve problems with fellow engineers.

Design Support *TI's Design Support* Quickly find helpful E2E forums along with design support tools and contact information for technical support.

11.5 商标

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11.6 静电放电警告

ESD 可能会损坏该集成电路。德州仪器 (TI) 建议通过适当的预防措施处理所有集成电路。如果不遵守正确的处理措施和安装程序，可能会损坏集成电路。

ESD 的损坏小至导致微小的性能降级，大至整个器件故障。 精密的集成电路可能更容易受到损坏，这是因为非常细微的参数更改都可能会导致器件与其发布的规格不相符。

11.7 术语表

SLYZ022 — *TI 术语表*。
    这份术语表列出并解释术语、缩写和定义。

12 机械、封装和可订购信息

以下页面包含机械、封装和可订购信息。这些信息是指定器件的最新可用数据。数据如有变更，恕不另行通知，且不会对此文档进行修订。如需获取此数据表的浏览器版本，请查阅左侧的导航栏。

PACKAGING INFORMATION

Orderable Device	Status (1)	Package Type	Package Drawing	Pins	Package Qty	Eco Plan (2)	Lead finish/ Ball material (6)	MSL Peak Temp (3)	Op Temp (°C)	Device Marking (4/5)	Samples
TLV76701DGNR	PREVIEW	HVSSOP	DGN	8	2500	Non-RoHS & Non-Green	Call TI	Call TI	-40 to 125		
TLV76701DRVR	ACTIVE	WSON	DRV	6	3000	RoHS & Green	NIPDAU | NIPDAUAG	Level-2-260C-1 YEAR	-40 to 125	1RMH	Samples
TLV76701DRVT	ACTIVE	WSON	DRV	6	250	RoHS & Green	NIPDAU | NIPDAUAG	Level-2-260C-1 YEAR	-40 to 125	1RMH	Samples
TLV76708DGNR	PREVIEW	HVSSOP	DGN	8	2500	Non-RoHS & Non-Green	Call TI	Call TI	-40 to 125		
TLV76708DRVR	ACTIVE	WSON	DRV	6	3000	RoHS & Green	NIPDAU | NIPDAUAG	Level-2-260C-1 YEAR	-40 to 125	1RNH	Samples
TLV76708DRVT	ACTIVE	WSON	DRV	6	250	RoHS & Green	NIPDAU | NIPDAUAG	Level-2-260C-1 YEAR	-40 to 125	1RNH	Samples
TLV76718DGNR	ACTIVE	HVSSOP	DGN	8	2500	RoHS & Green	NIPDAUAG	Level-2-260C-1 YEAR	-40 to 125	2BMX	Samples
TLV76718DRVR	ACTIVE	WSON	DRV	6	3000	RoHS & Green	NIPDAU | NIPDAUAG	Level-2-260C-1 YEAR	-40 to 125	1ROH	Samples
TLV76718DRVT	ACTIVE	WSON	DRV	6	250	RoHS & Green	NIPDAU | NIPDAUAG	Level-2-260C-1 YEAR	-40 to 125	1ROH	Samples
TLV76725DGNR	ACTIVE	HVSSOP	DGN	8	2500	RoHS & Green	NIPDAUAG	Level-2-260C-1 YEAR	-40 to 125	2GT7	Samples
TLV76728DGNR	ACTIVE	HVSSOP	DGN	8	2500	RoHS & Green	NIPDAUAG	Level-2-260C-1 YEAR	-40 to 125	2BNX	Samples
TLV76728DRVR	ACTIVE	WSON	DRV	6	3000	RoHS & Green	NIPDAU | NIPDAUAG	Level-2-260C-1 YEAR	-40 to 125	1RPH	Samples
TLV76728DRVT	ACTIVE	WSON	DRV	6	250	RoHS & Green	NIPDAU | NIPDAUAG	Level-2-260C-1 YEAR	-40 to 125	1RPH	Samples
TLV76733DGNR	ACTIVE	HVSSOP	DGN	8	2500	RoHS & Green	NIPDAUAG	Level-2-260C-1 YEAR	-40 to 125	2BOX	Samples
TLV76733DRVR	ACTIVE	WSON	DRV	6	3000	RoHS & Green	NIPDAU | NIPDAUAG	Level-2-260C-1 YEAR	-40 to 125	1RQH	Samples
TLV76733DRVT	ACTIVE	WSON	DRV	6	250	RoHS & Green	NIPDAU | NIPDAUAG	Level-2-260C-1 YEAR	-40 to 125	1RQH	Samples
TLV76750DGNR	ACTIVE	HVSSOP	DGN	8	2500	RoHS & Green	NIPDAUAG	Level-2-260C-1 YEAR	-40 to 125	2BPX	Samples
TLV76750DRVR	ACTIVE	WSON	DRV	6	3000	RoHS & Green	NIPDAU | NIPDAUAG	Level-2-260C-1 YEAR	-40 to 125	1RRH	Samples
TLV76750DRVT	ACTIVE	WSON	DRV	6	250	RoHS & Green	NIPDAU | NIPDAUAG	Level-2-260C-1 YEAR	-40 to 125	1RRH	Samples

(1) The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

OBSOLETE: TI has discontinued the production of the device.

(2) **RoHS:** TI defines "RoHS" to mean semiconductor products that are compliant with the current EU RoHS requirements for all 10 RoHS substances, including the requirement that RoHS substance do not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, "RoHS" products are suitable for use in specified lead-free processes. TI may reference these types of products as "Pb-Free".

RoHS Exempt: TI defines "RoHS Exempt" to mean products that contain lead but are compliant with EU RoHS pursuant to a specific EU RoHS exemption.

Green: TI defines "Green" to mean the content of Chlorine (Cl) and Bromine (Br) based flame retardants meet JS709B low halogen requirements of <=1000ppm threshold. Antimony trioxide based flame retardants must also meet the <=1000ppm threshold requirement.

(3) MSL, Peak Temp. - The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

(4) There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.

(5) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.

(6) Lead finish/Ball material - Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

Important Information and Disclaimer: The information provided on this page represents TI's knowledge and belief as of the date that it is provided. TI bases its knowledge and belief on information provided by third parties, and makes no representation or warranty as to the accuracy of such information. Efforts are underway to better integrate information from third parties. TI has taken and continues to take reasonable steps to provide representative and accurate information but may not have conducted destructive testing or chemical analysis on incoming materials and chemicals. TI and TI suppliers consider certain information to be proprietary, and thus CAS numbers and other limited information may not be available for release.

In no event shall TI's liability arising out of such information exceed the total purchase price of the TI part(s) at issue in this document sold by TI to Customer on an annual basis.

OTHER QUALIFIED VERSIONS OF TLV767 :

- Automotive : TLV767-Q1

NOTE: Qualified Version Definitions:

- Automotive - Q100 devices qualified for high-reliability automotive applications targeting zero defects

PACKAGE MATERIALS INFORMATION

TAPE AND REEL INFORMATION

REEL DIMENSIONS

TAPE DIMENSIONS

A0	Dimension designed to accommodate the component width
B0	Dimension designed to accommodate the component length
K0	Dimension designed to accommodate the component thickness
W	Overall width of the carrier tape
P1	Pitch between successive cavity centers

QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE

*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
TLV76701DRVR	WSON	DRV	6	3000	180.0	8.4	2.3	2.3	1.15	4.0	8.0	Q2
TLV76701DRVT	WSON	DRV	6	250	180.0	8.4	2.3	2.3	1.15	4.0	8.0	Q2
TLV76708DRVR	WSON	DRV	6	3000	180.0	8.4	2.3	2.3	1.15	4.0	8.0	Q2
TLV76708DRVR	WSON	DRV	6	3000	178.0	8.4	2.25	2.25	1.0	4.0	8.0	Q2
TLV76708DRVT	WSON	DRV	6	250	180.0	8.4	2.3	2.3	1.15	4.0	8.0	Q2
TLV76708DRVT	WSON	DRV	6	250	178.0	8.4	2.25	2.25	1.0	4.0	8.0	Q2
TLV76718DGNR	HVSSOP	DGN	8	2500	330.0	12.4	5.3	3.4	1.4	8.0	12.0	Q1
TLV76718DRVR	WSON	DRV	6	3000	178.0	8.4	2.25	2.25	1.0	4.0	8.0	Q2
TLV76718DRVR	WSON	DRV	6	3000	180.0	8.4	2.3	2.3	1.15	4.0	8.0	Q2
TLV76718DRVT	WSON	DRV	6	250	180.0	8.4	2.3	2.3	1.15	4.0	8.0	Q2
TLV76718DRVT	WSON	DRV	6	250	178.0	8.4	2.25	2.25	1.0	4.0	8.0	Q2
TLV76725DGNR	HVSSOP	DGN	8	2500	330.0	12.4	5.3	3.4	1.4	8.0	12.0	Q1
TLV76728DGNR	HVSSOP	DGN	8	2500	330.0	12.4	5.3	3.4	1.4	8.0	12.0	Q1
TLV76728DRVR	WSON	DRV	6	3000	180.0	8.4	2.3	2.3	1.15	4.0	8.0	Q2
TLV76728DRVR	WSON	DRV	6	3000	178.0	8.4	2.25	2.25	1.0	4.0	8.0	Q2
TLV76728DRVT	WSON	DRV	6	250	178.0	8.4	2.25	2.25	1.0	4.0	8.0	Q2
TLV76728DRVT	WSON	DRV	6	250	180.0	8.4	2.3	2.3	1.15	4.0	8.0	Q2
TLV76733DGNR	HVSSOP	DGN	8	2500	330.0	12.4	5.3	3.4	1.4	8.0	12.0	Q1

Device	Package Type	Package Drawing	Pins	SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
TLV76733DRVR	WSON	DRV	6	3000	178.0	8.4	2.25	2.25	1.0	4.0	8.0	Q2
TLV76733DRVR	WSON	DRV	6	3000	180.0	8.4	2.3	2.3	1.15	4.0	8.0	Q2
TLV76733DRVT	WSON	DRV	6	250	178.0	8.4	2.25	2.25	1.0	4.0	8.0	Q2
TLV76733DRVT	WSON	DRV	6	250	180.0	8.4	2.3	2.3	1.15	4.0	8.0	Q2
TLV76750DGNR	HVSSOP	DGN	8	2500	330.0	12.4	5.3	3.4	1.4	8.0	12.0	Q1
TLV76750DRVR	WSON	DRV	6	3000	178.0	8.4	2.25	2.25	1.0	4.0	8.0	Q2
TLV76750DRVR	WSON	DRV	6	3000	180.0	8.4	2.3	2.3	1.15	4.0	8.0	Q2
TLV76750DRVT	WSON	DRV	6	250	180.0	8.4	2.3	2.3	1.15	4.0	8.0	Q2
TLV76750DRVT	WSON	DRV	6	250	178.0	8.4	2.25	2.25	1.0	4.0	8.0	Q2

TAPE AND REEL BOX DIMENSIONS
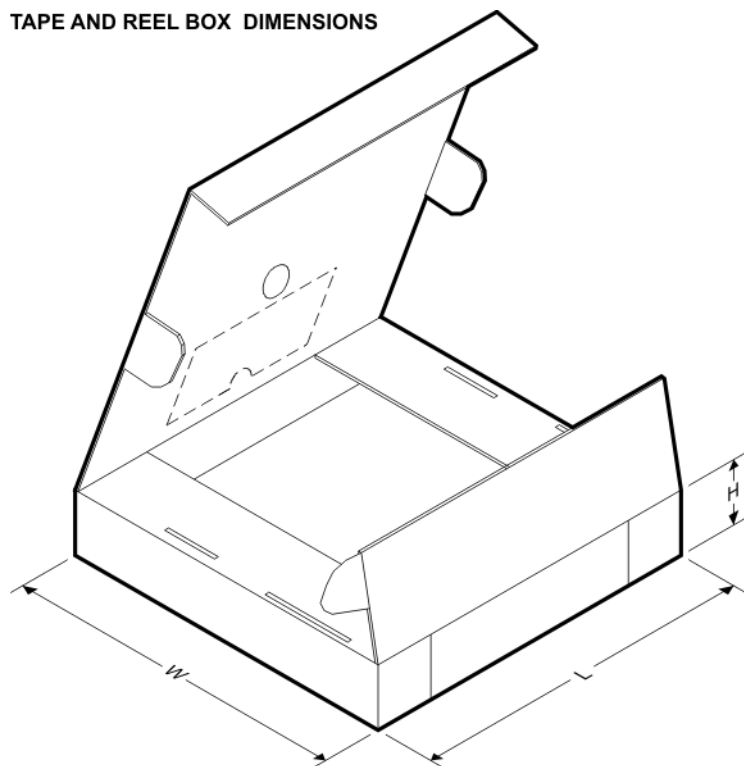
*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
TLV76701DRVR	WSON	DRV	6	3000	210.0	185.0	35.0
TLV76701DRVT	WSON	DRV	6	250	210.0	185.0	35.0
TLV76708DRVR	WSON	DRV	6	3000	210.0	185.0	35.0
TLV76708DRVR	WSON	DRV	6	3000	205.0	200.0	33.0
TLV76708DRVT	WSON	DRV	6	250	210.0	185.0	35.0
TLV76708DRVT	WSON	DRV	6	250	205.0	200.0	33.0
TLV76718DGNR	HVSSOP	DGN	8	2500	366.0	364.0	50.0
TLV76718DRVR	WSON	DRV	6	3000	205.0	200.0	33.0

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
TLV76718DRVR	WSON	DRV	6	3000	210.0	185.0	35.0
TLV76718DRVT	WSON	DRV	6	250	210.0	185.0	35.0
TLV76718DRVT	WSON	DRV	6	250	205.0	200.0	33.0
TLV76725DGNR	HVSSOP	DGN	8	2500	366.0	364.0	50.0
TLV76728DGNR	HVSSOP	DGN	8	2500	366.0	364.0	50.0
TLV76728DRVR	WSON	DRV	6	3000	210.0	185.0	35.0
TLV76728DRVR	WSON	DRV	6	3000	205.0	200.0	33.0
TLV76728DRVT	WSON	DRV	6	250	205.0	200.0	33.0
TLV76728DRVT	WSON	DRV	6	250	210.0	185.0	35.0
TLV76733DGNR	HVSSOP	DGN	8	2500	366.0	364.0	50.0
TLV76733DRVR	WSON	DRV	6	3000	205.0	200.0	33.0
TLV76733DRVR	WSON	DRV	6	3000	210.0	185.0	35.0
TLV76733DRVT	WSON	DRV	6	250	205.0	200.0	33.0
TLV76733DRVT	WSON	DRV	6	250	210.0	185.0	35.0
TLV76750DGNR	HVSSOP	DGN	8	2500	366.0	364.0	50.0
TLV76750DRVR	WSON	DRV	6	3000	205.0	200.0	33.0
TLV76750DRVR	WSON	DRV	6	3000	210.0	185.0	35.0
TLV76750DRVT	WSON	DRV	6	250	210.0	185.0	35.0
TLV76750DRVT	WSON	DRV	6	250	205.0	200.0	33.0

Images above are just a representation of the package family, actual package may vary.
Refer to the product data sheet for package details.

4206925/F

2.1
1.9

2.1
1.9

PIN 1 INDEX AREA

0.8
0.7

SEATING PLANE

0.08 C

EXPOSED
THERMAL PAD

1±0.1

2X
1.3

1.6±0.1

4X 0.65

PIN 1 ID
(OPTIONAL)

6X 0.3
0.2

6X 0.35
0.25

0.1 M C A S B S
0.05 M C

0.05
0.00

(0.2) TYP
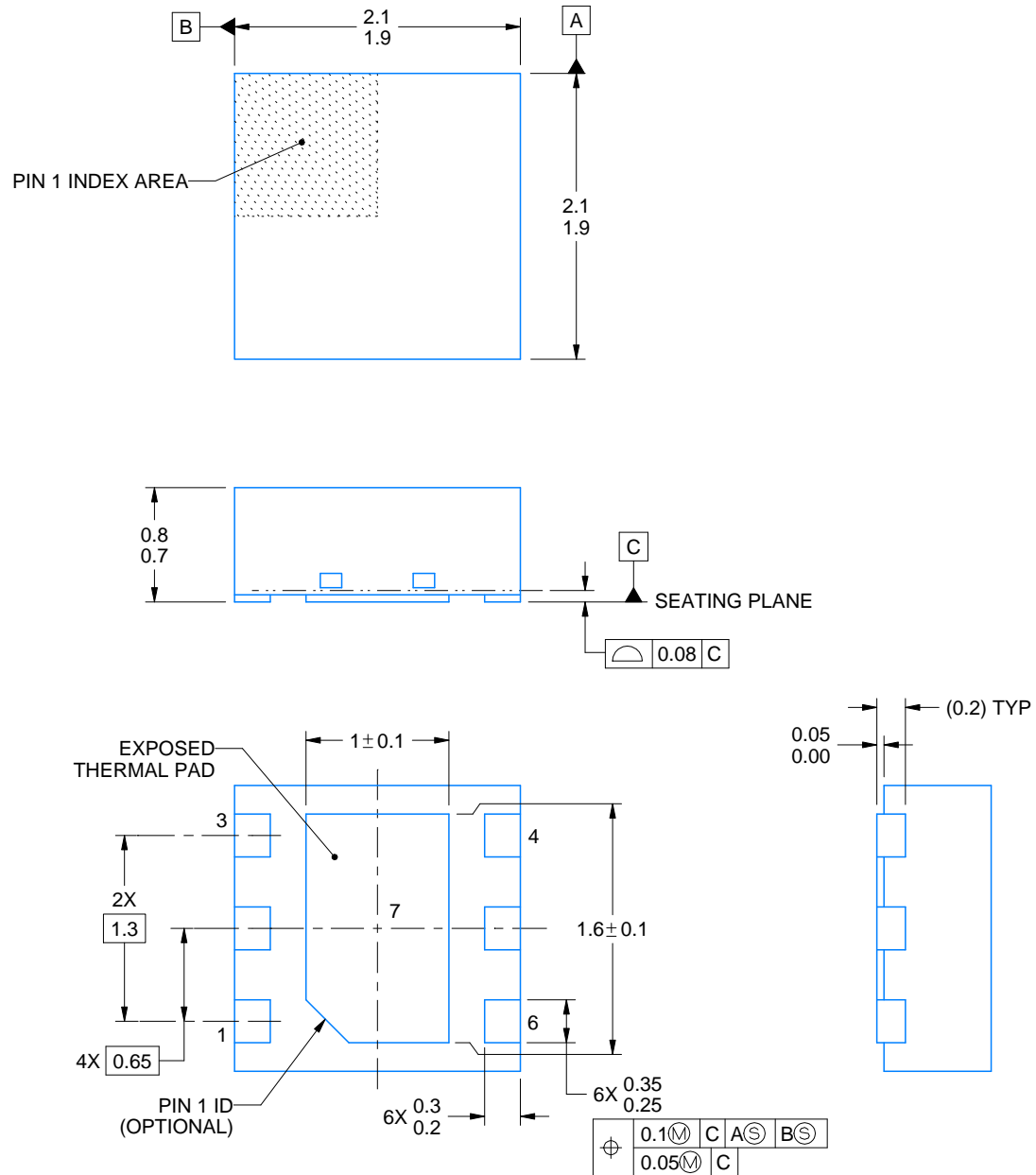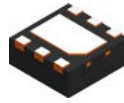
4222173/B   04/2018

NOTES:

1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
2. This drawing is subject to change without notice.
3. The package thermal pad must be soldered to the printed circuit board for thermal and mechanical performance.

6X (0.45)

6X (0.3)

(1)

7

6

SYMM
℄

(1.6)

(1.1)

4X (0.65)

3

4

SYMM
℄

(R0.05) TYP

(⌀ 0.2) VIA
TYP

(1.95)

LAND PATTERN EXAMPLE
SCALE:25X

0.07 MAX
ALL AROUND

0.07 MIN
ALL AROUND

SOLDER MASK
OPENING

METAL

METAL UNDER
SOLDER MASK

SOLDER MASK
OPENING

NON SOLDER MASK
DEFINED
(PREFERRED)

SOLDER MASK
DEFINED

SOLDER MASK DETAILS

4222173/B 04/2018

NOTES: (continued)

4. This package is designed to be soldered to a thermal pad on the board. For more information, see Texas Instruments literature number SLUA271 (www.ti.com/lit/slua271).
5. Vias are optional depending on application, refer to device data sheet. If some or all are implemented, recommended via locations are shown.

SYMM

METAL

6X (0.45)

1

6X (0.3)

7

6

(0.45)

SYMM

4X (0.65)

(0.7)

3

4

(R0.05) TYP

(1)

(1.95)
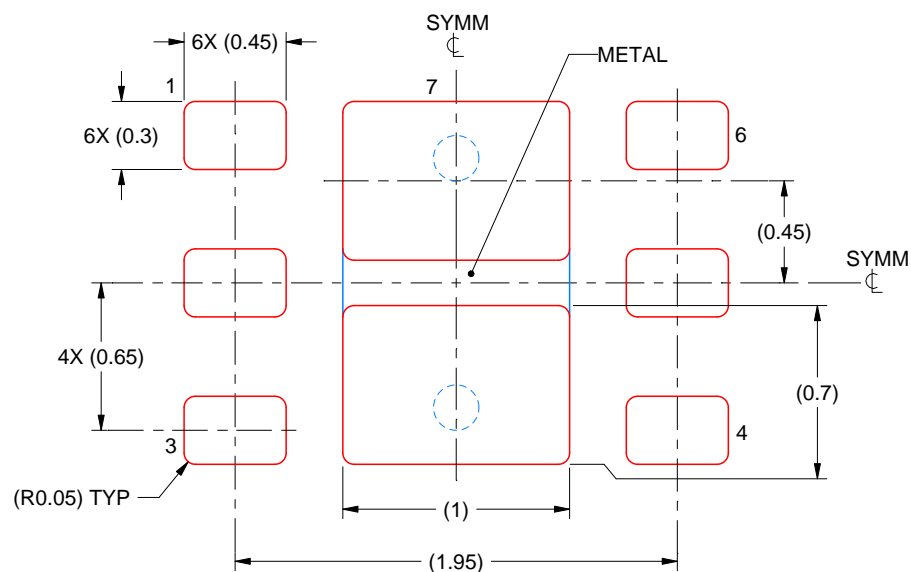
SOLDER PASTE EXAMPLE
BASED ON 0.125 mm THICK STENCIL

EXPOSED PAD #7
88% PRINTED SOLDER COVERAGE BY AREA UNDER PACKAGE
SCALE:30X

4222173/B   04/2018

NOTES: (continued)

6. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
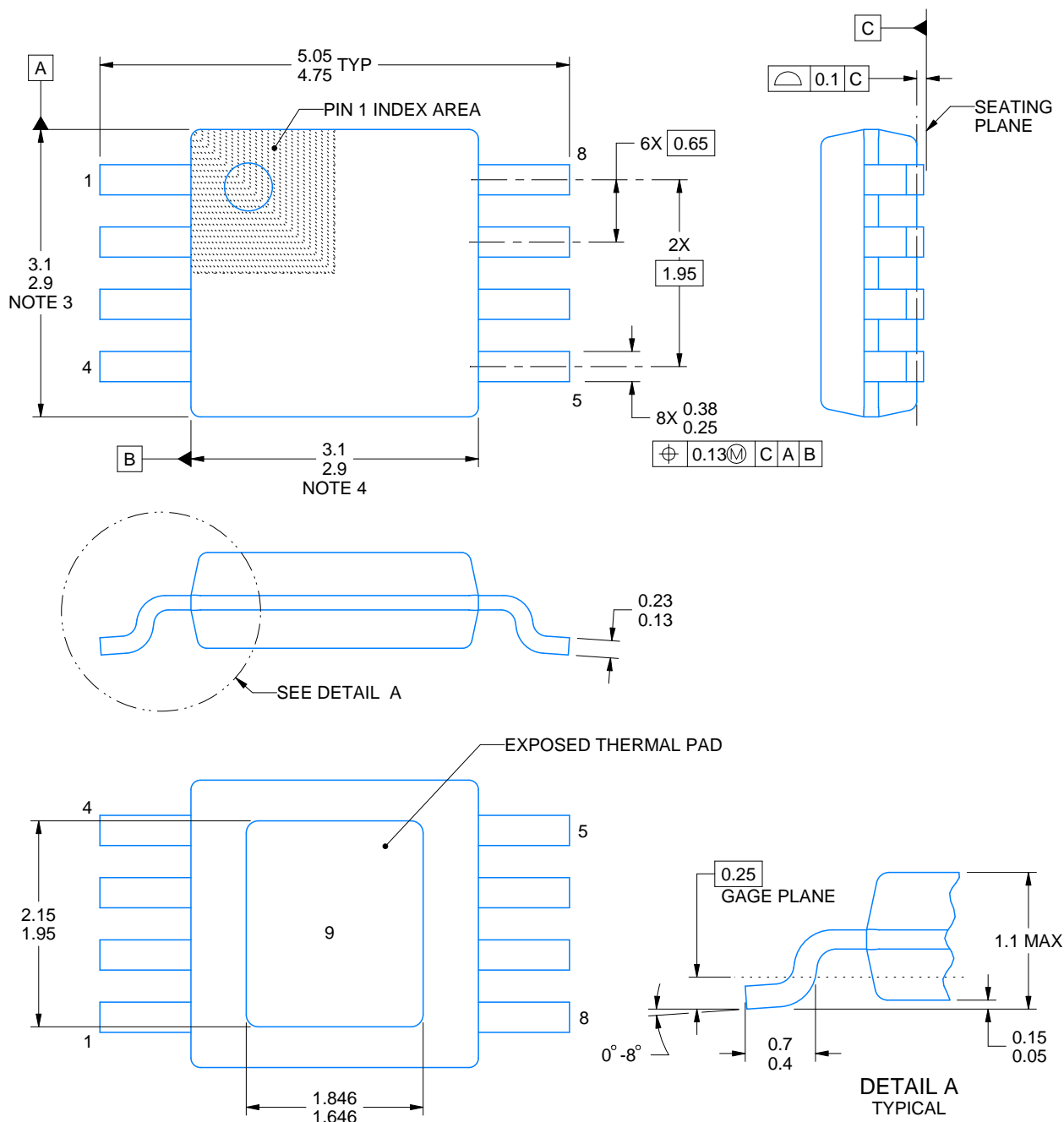
DGN 8
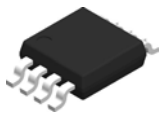
PowerPAD™ VSSOP - 1.1 mm max height

3 x 3, 0.65 mm pitch

SMALL OUTLINE PACKAGE

This image is a representation of the package family, actual package may vary.
Refer to the product data sheet for package details.

4225482/A

4225480/A   11/2019
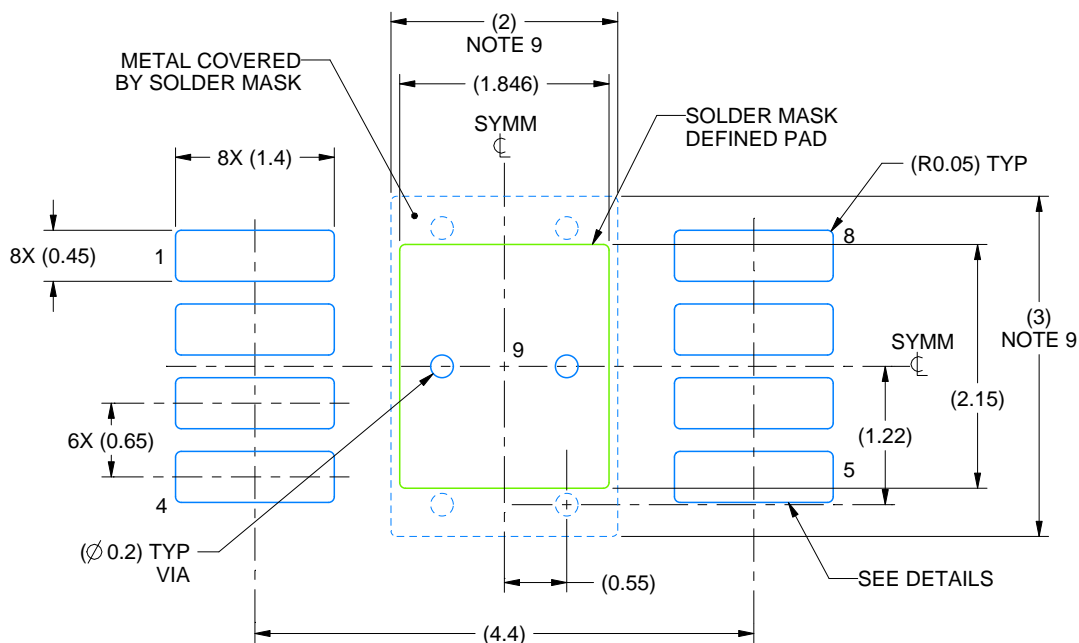
PowerPAD is a trademark of Texas Instruments.

NOTES:

1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
2. This drawing is subject to change without notice.
3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0.15 mm per side.
4. This dimension does not include interlead flash. Interlead flash shall not exceed 0.25 mm per side.
5. Reference JEDEC registration MO-187.

DGN0008G

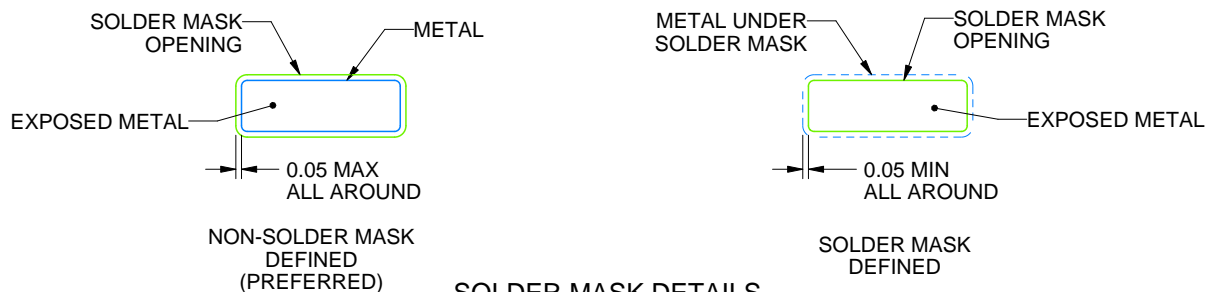## PowerPAD™ VSSOP - 1.1 mm max height

METAL COVERED
BY SOLDER MASK

(2)
NOTE 9

(1.846)

SYMM

SOLDER MASK
DEFINED PAD

(R0.05) TYP

8X (1.4)

8X (0.45)   1

8

(3)
NOTE 9

SYMM

(2.15)

9

(1.22)

6X (0.65)

4

5

(Ø 0.2) TYP
VIA

SEE DETAILS

(0.55)

(4.4)

LAND PATTERN EXAMPLE
EXPOSED METAL SHOWN
SCALE: 15X

SOLDER MASK
OPENING

METAL

METAL UNDER
SOLDER MASK

SOLDER MASK
OPENING

EXPOSED METAL

EXPOSED METAL

0.05 MAX
ALL AROUND

0.05 MIN
ALL AROUND

NON-SOLDER MASK
DEFINED
(PREFERRED)

SOLDER MASK
DEFINED

SOLDER MASK DETAILS

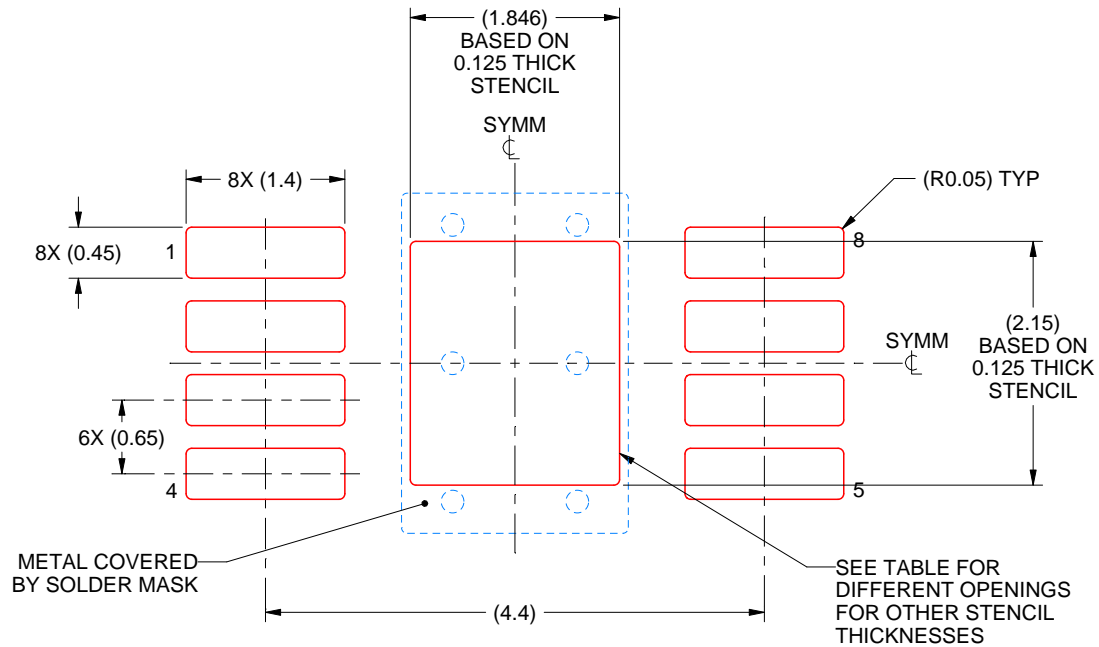4225480/A   11/2019

NOTES: (continued)

6. Publication IPC-7351 may have alternate designs.
7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.
8. Vias are optional depending on application, refer to device data sheet. If any vias are implemented, refer to their locations shown
   on this view. It is recommended that vias under paste be filled, plugged or tented.
9. Size of metal pad may vary due to creepage requirement.

(1.846)
BASED ON
0.125 THICK
STENCIL

SYMM

8X (1.4)

8X (0.45)   1

(R0.05) TYP

8

SYMM

(2.15)
BASED ON
0.125 THICK
STENCIL

6X (0.65)

4

5

METAL COVERED
BY SOLDER MASK

SEE TABLE FOR
DIFFERENT OPENINGS
FOR OTHER STENCIL
THICKNESSES

(4.4)

SOLDER PASTE EXAMPLE
EXPOSED PAD 9:
100% PRINTED SOLDER COVERAGE BY AREA
SCALE: 15X

STENCIL THICKNESS	SOLDER STENCIL OPENING
0.1	2.06 X 2.40
0.125	1.846 X 2.15 (SHOWN)
0.15	1.69 X 1.96
0.175	1.56 X 1.82

4225480/A   11/2019

NOTES: (continued)

10. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
11. Board assembly site may have different recommendations for stencil design.

重要声明和免责声明